



**CSST**

Chair of Computational Science  
and Simulation Technology



Leibniz  
Universität  
Hannover

# Multiscale Modelling and Optimization of Flexoelectric Nano Structures

Xiaoying Zhuang

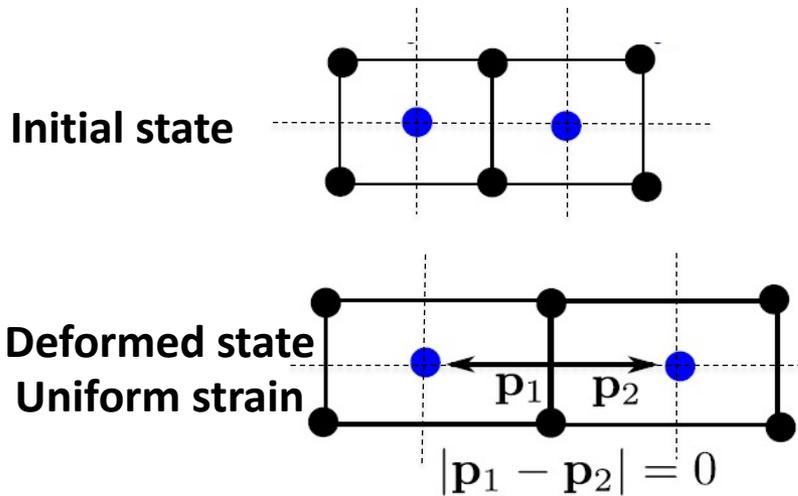
Faculty of Mathematics and Physics  
Leibniz University Hannover  
Hannover Center for Optical Technology

Jan 20 2022

# Piezoelectricity V.S. flexoelectricity

## Centrosymmetric crystals

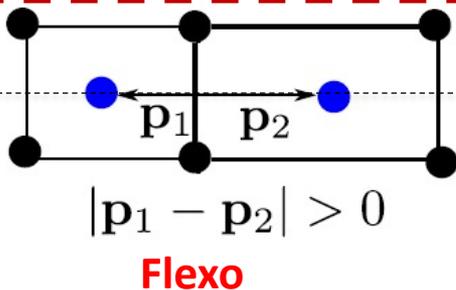
All type of materials



$$P^\alpha = \underbrace{\mu^{\alpha\beta\gamma\delta} \frac{\partial \epsilon^{\gamma\delta}}{\partial x_\beta}}_{\text{Flexo}} + \underbrace{d^{\alpha\beta\gamma} \epsilon^{\beta\gamma}}_{\text{Piezo}}$$

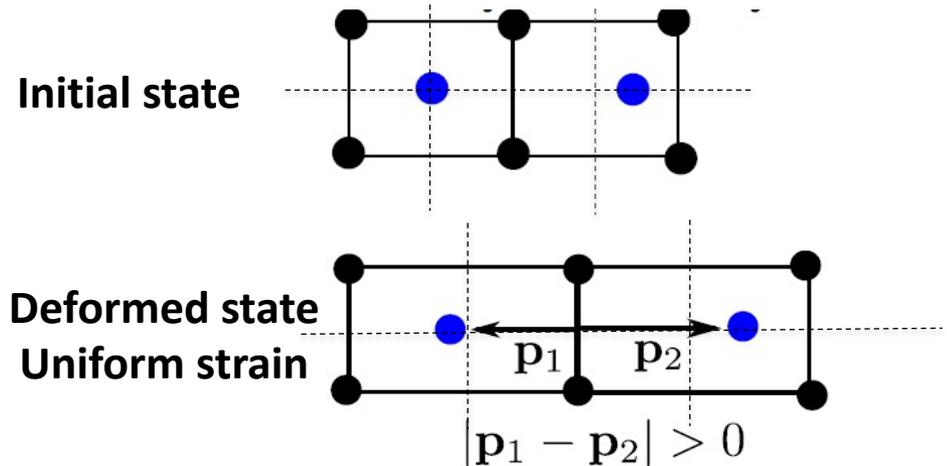
**Flexo**

Deformed state  
Strain gradient



## Non-centrosymmetric crystals

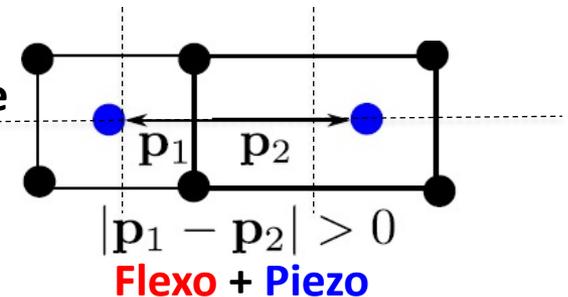
Quartz, ZnO, Sucrose, Lead titanate, bone, DNA



**Piezo**

**Piezo**

Deformed state  
Strain gradient

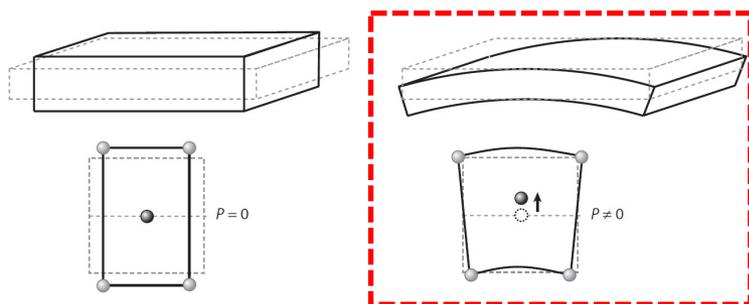


Inhomogeneous deformation



Strain engineering

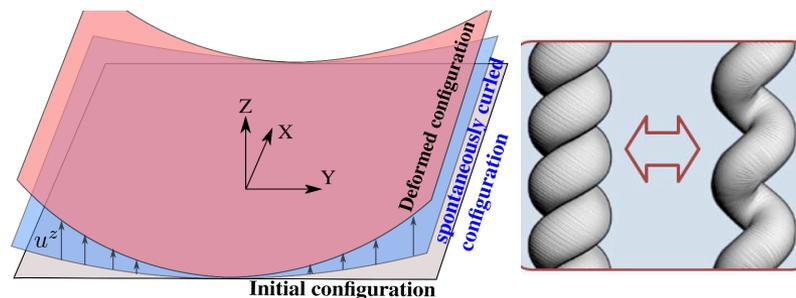
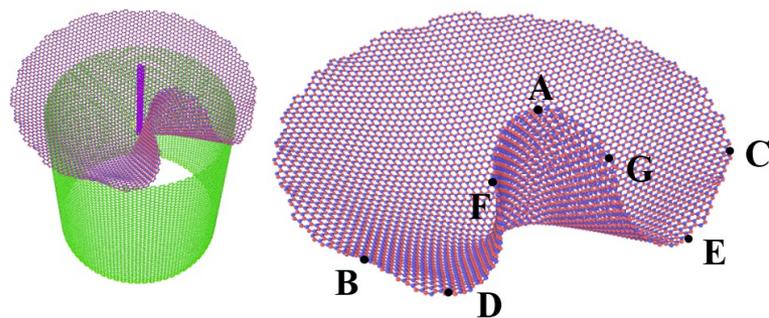
WHAT is FLEXOELECTRICITY?



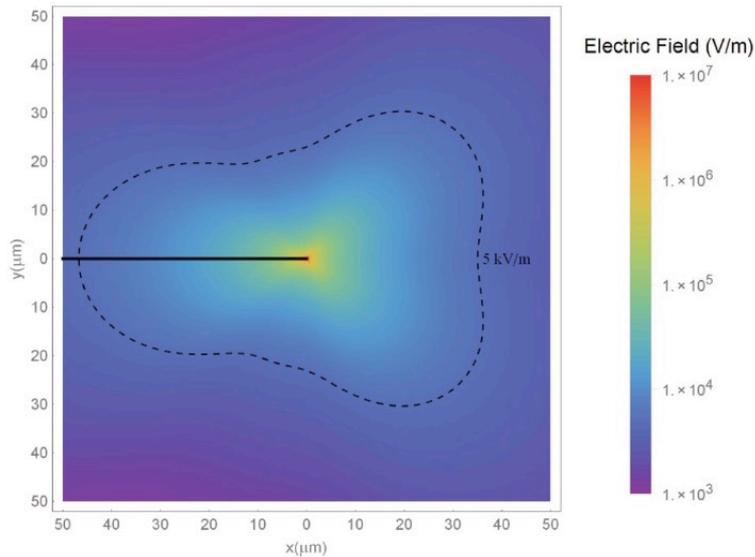
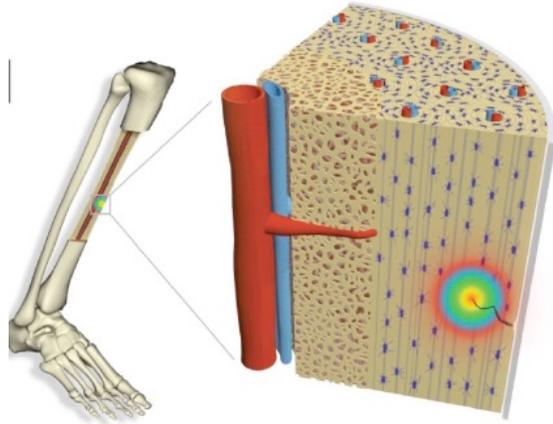
$$P_3 = \mu_{12} \frac{\partial \epsilon_{11}}{\partial x_3}$$

Gradient of strain!

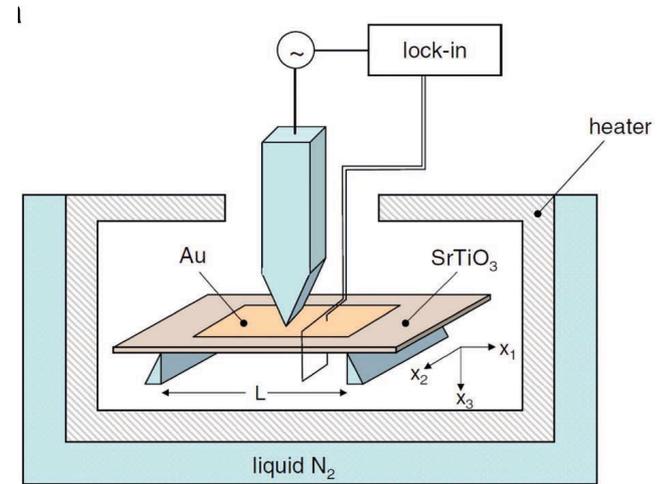
Bending, crumpling, torsion...



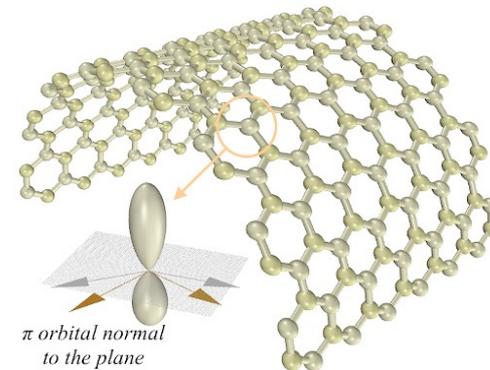
# Where does flexoelectricity exist?



Flexoelectricity around a microcrack  
bone model



Crystalline material e.g. STO by bending induced  
flexoelectricity



In graphene by breaking symmetry

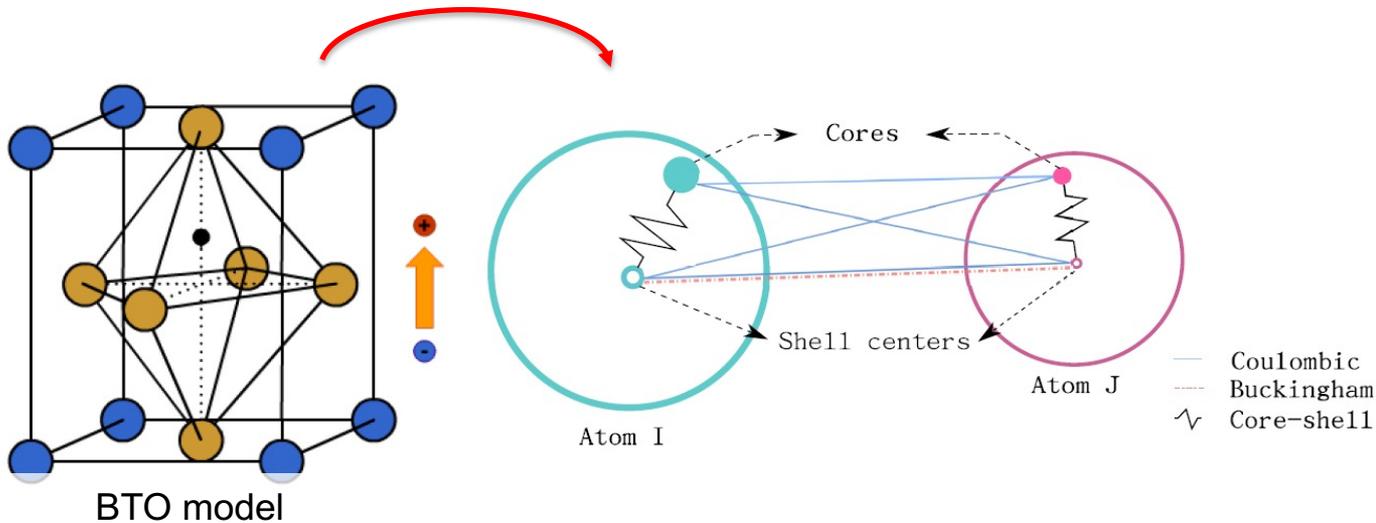
- Flexoelectric parameters are unclear
- Many phenomena are not understood: surface piezo, surface flexo, free charge carriers...
- *HOW* to engineer and optimize flexoelectricity?  
*Lack of physical model and simulation tool!*

## Inconsistent results?

	Barium Titanate (BTO)	
	$\mu_{11}$ (nC/m)	$\mu_{12}$ (nC/m)
Cross [Experiment]	---	9508~10980
Sharma [Lattice dynamics]	0.15	-5.46
Tao [First principle]	-0.36	1.6
Vanderbilt [First principle]	-334.3	13.8

- **Atomic-scale** model of flexoelectric materials
- **Nano-continuum scale** model of flexoelectric structures
- **Microscale** model of flexoelectric composites
- **Macroscale** application with phonic topological insulator





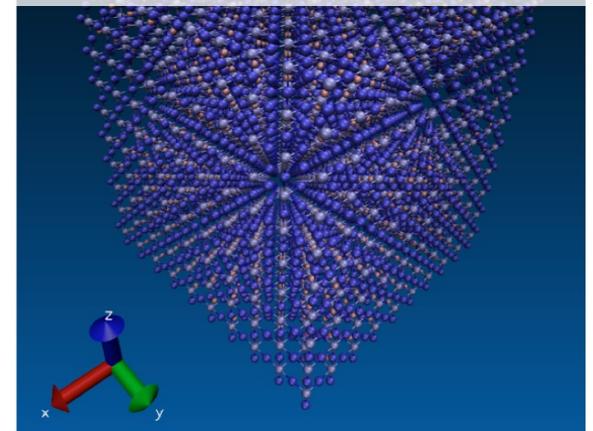
Buckingham short range potential

Long range Coulombic potential

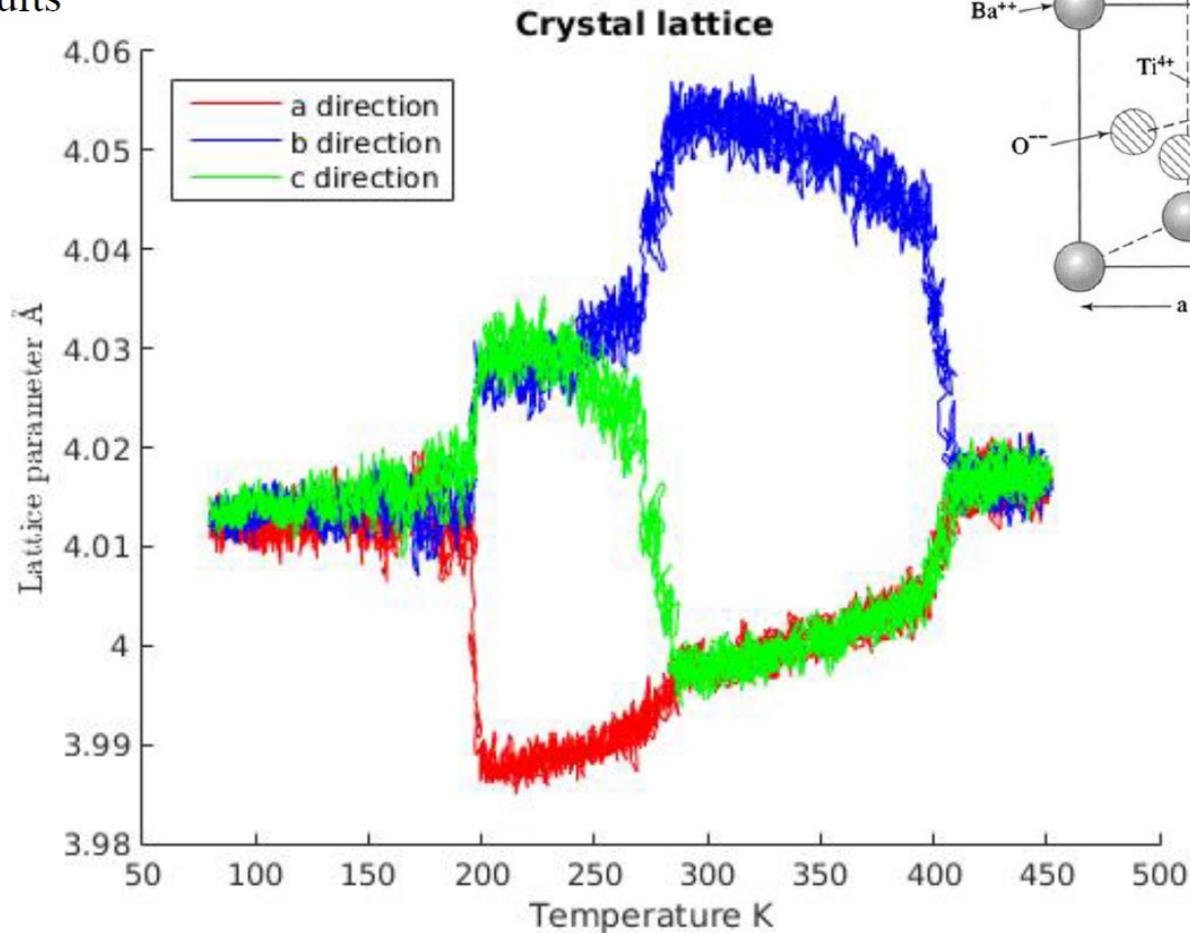
$$E_{total}(\mathbf{r}_{ij}) = \sum_{i=1}^N \sum_{i \neq j} \left\{ A_{ij} \exp\left(\frac{r_{ij}}{\rho}\right) - \frac{B_{ij}}{r_{ij}^6} \right\} + \frac{q_i q_j}{4\pi\epsilon_0 r_{ij}}$$

$$+ \frac{1}{2} k_2 |\mathbf{r}_{ij}^2| + \frac{1}{24} k_4 |\mathbf{r}_{ij}^4|$$

BTO atomistic model

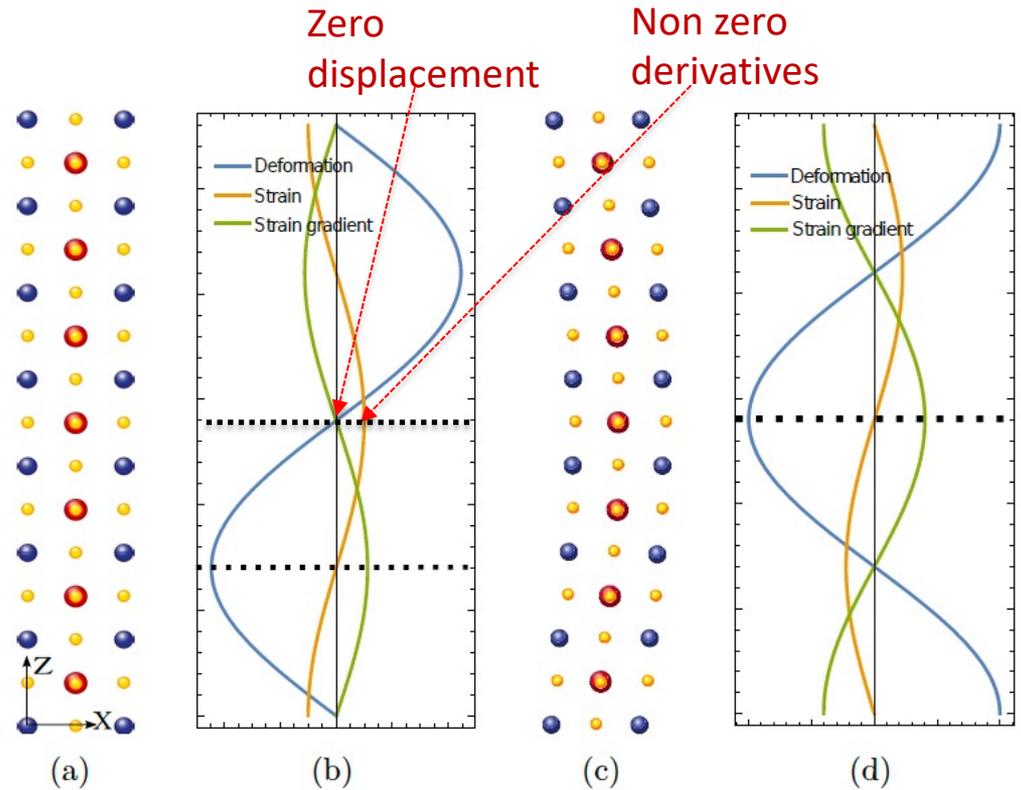
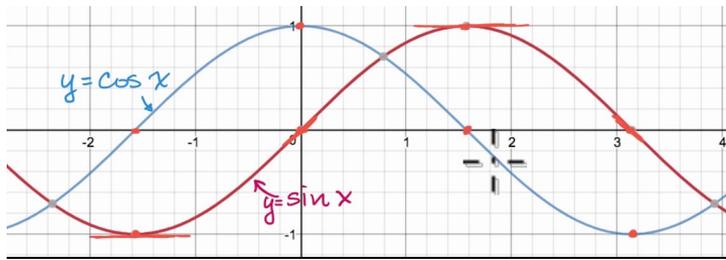


## Results



# Extraction of flexo parameters

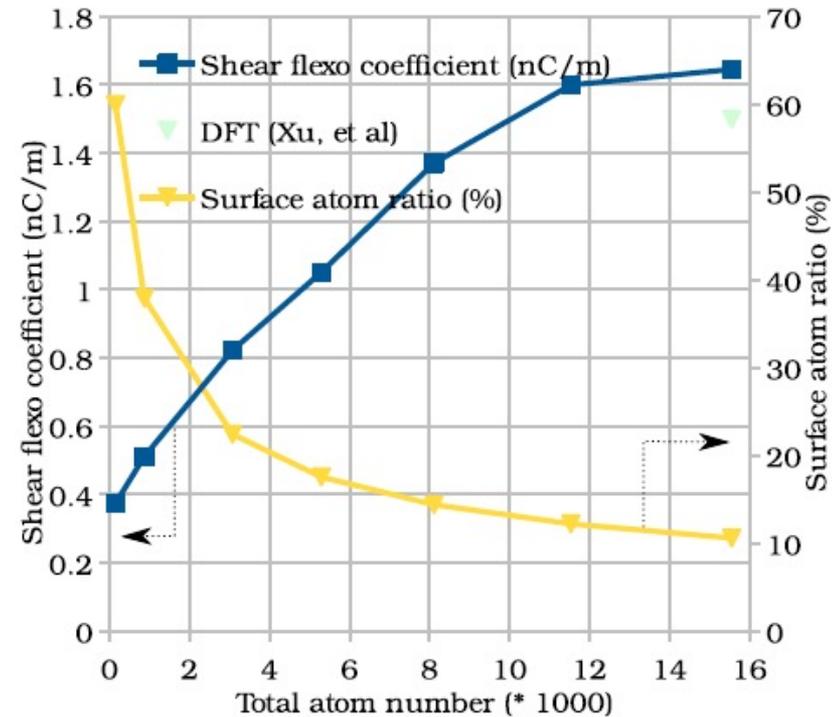
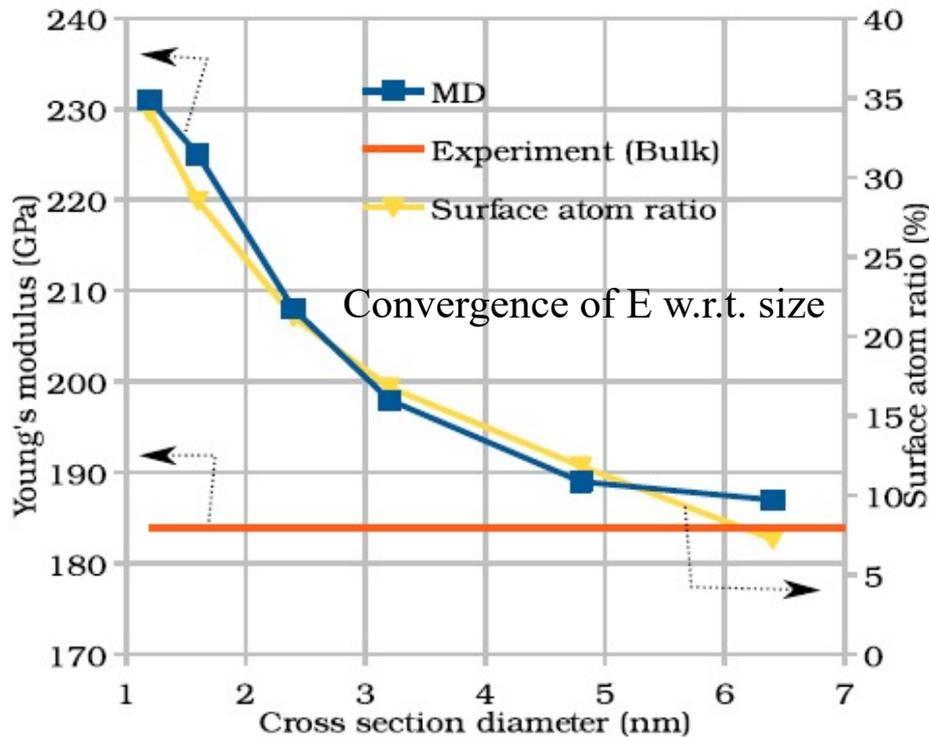
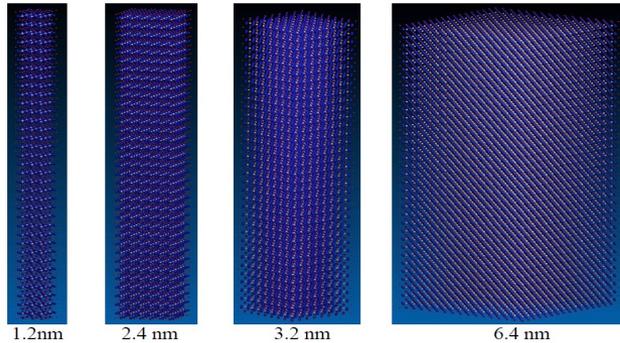
$$\delta^{long}(z) = \frac{\epsilon_{max} h}{2\pi} \sin\left(\frac{2\pi z}{h}\right),$$



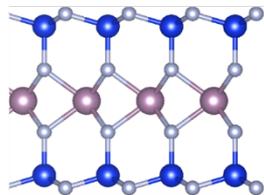
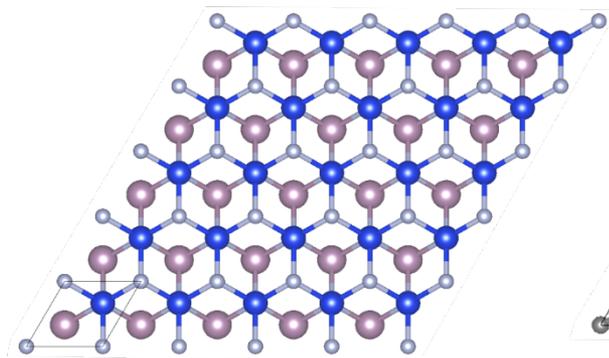
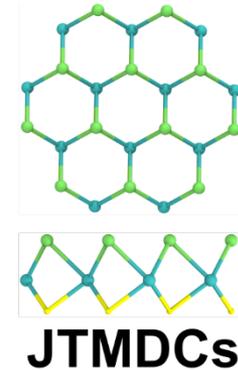
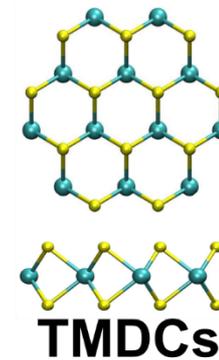
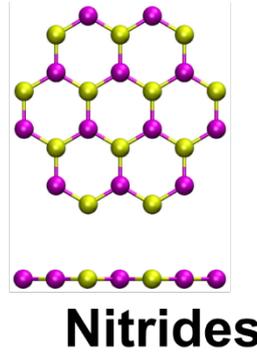
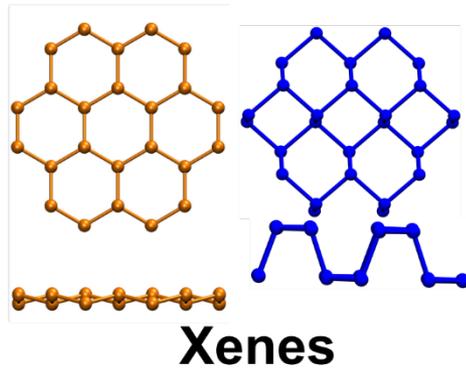
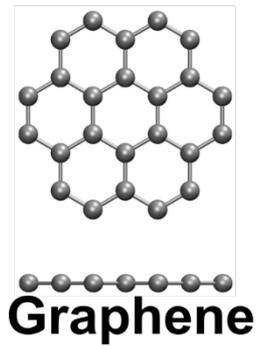
Imposition of sinusoidal boundary conditions to exclude piezoelectricity

# Size effects of BTO

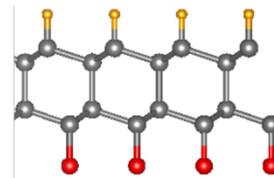
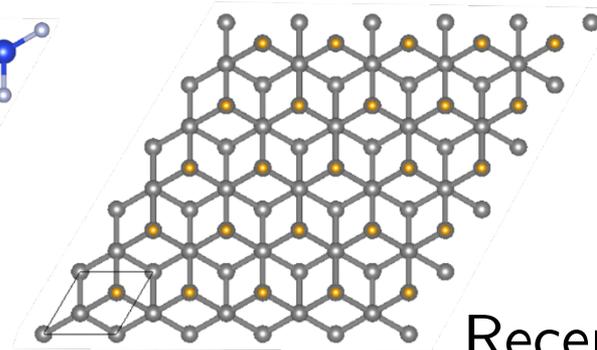
Size dependent Young's modulus (BTO nano-beam with different cross section size)



# Flexoelectricity in 2D materials

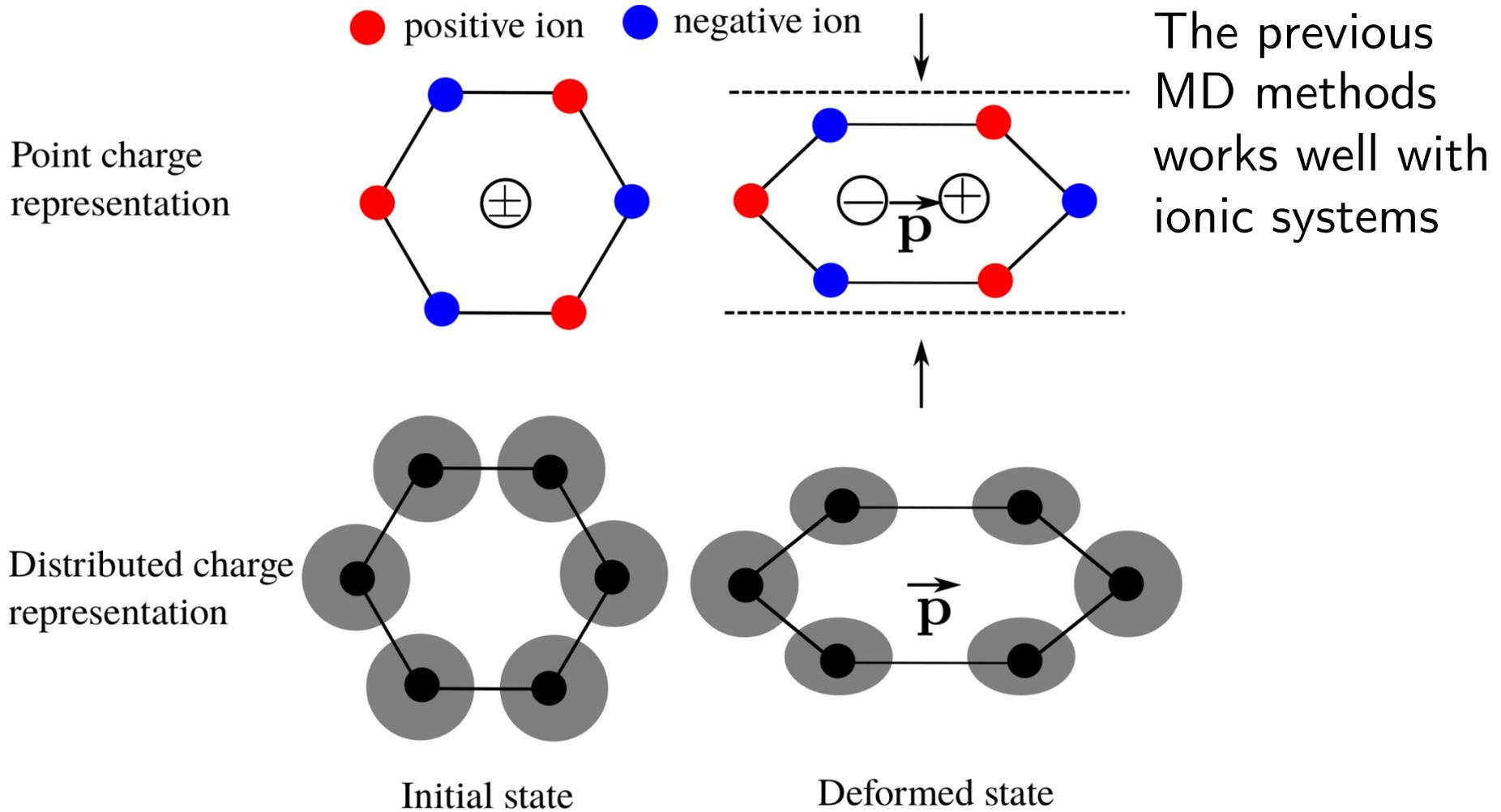


**MXT**



**Diamanes**

Recent experimentally synthesized 2D materials



They fail to investigate the systems with charge distributed (covalent or metallic systems)

We need a model that can handle

- Non-periodicity
- Dynamical changes in charges and dipoles
- Both small and large deformations
- Realistic loading conditions
- Works for any system (irrespective of bonding nature)

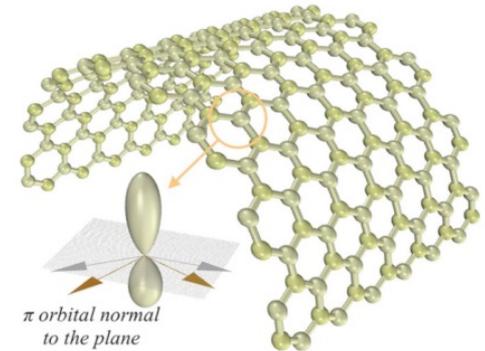
We developed a scheme that estimates the charges and dipoles (CD model) during the MD time integration

# Charge dipole model for graphene

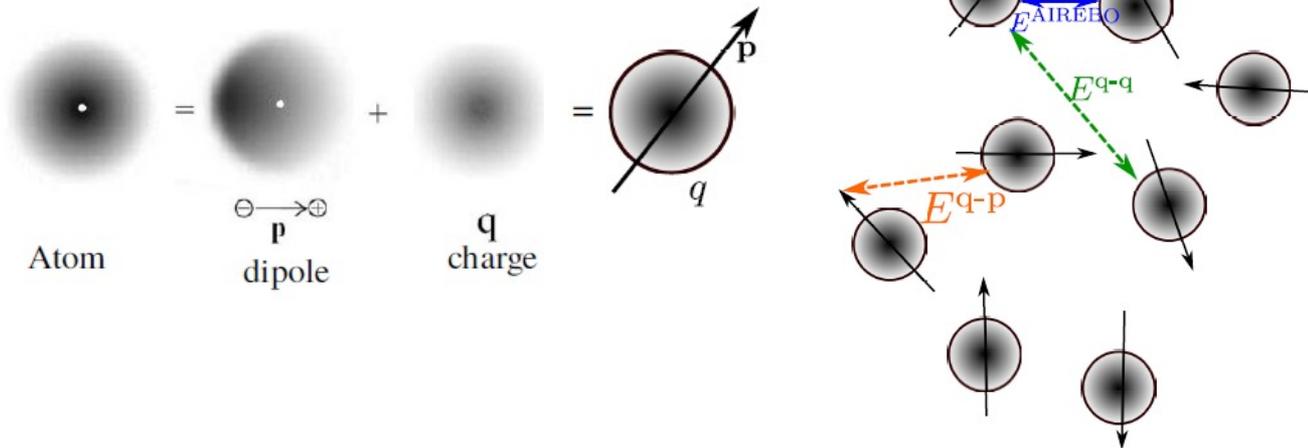
The total atomic interaction energy of Graphene system consist of short range and long range interaction.

$$E = E^{\text{AIREBO}} + \frac{E^{q-q} + E^{q-p} + E^{p-p} + E^{\text{ext}}}{\text{long range (charge-dipole)}}$$

short range
long range (charge-dipole)



## Charge-dipole scheme

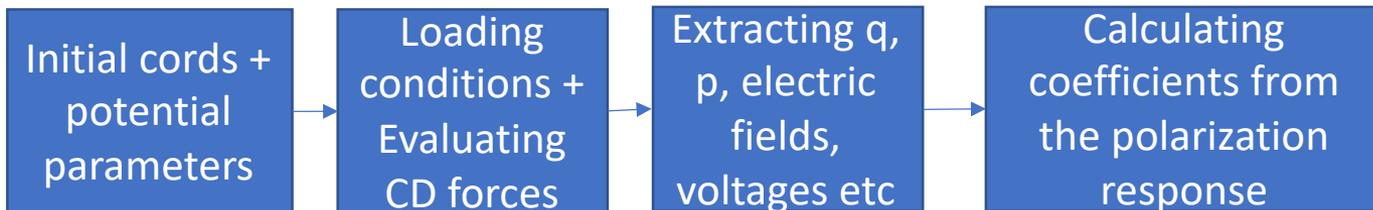
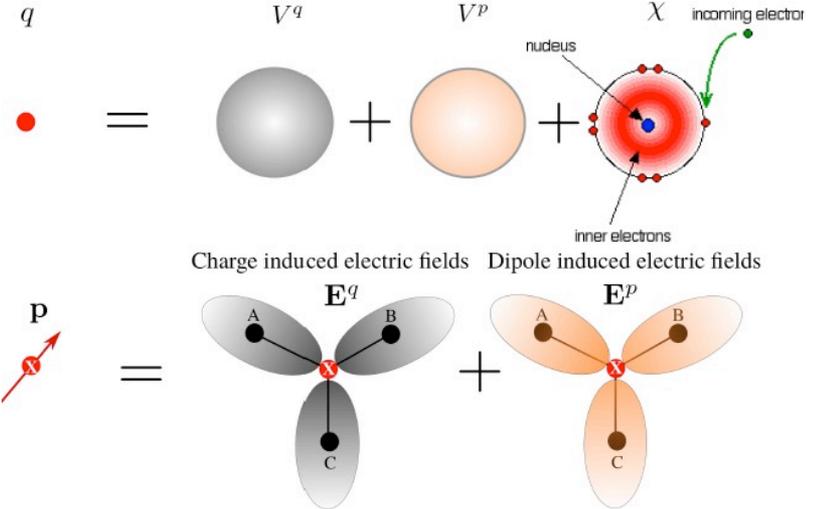


## Governing equation

$$m_i \ddot{\mathbf{r}}_i = - \frac{\partial E^{\text{Short-range}}}{\partial \mathbf{r}_i} - \frac{\partial E^{q-q}}{\partial \mathbf{r}_i} - \frac{\partial E^{q-p}}{\partial \mathbf{r}_i} - \frac{\partial E^{p-p}}{\partial \mathbf{r}_i}$$

$$\sum_{j=1; i \neq j}^N T_{ij}^{q-q} q_j - \sum_{j=1; i \neq j}^N T_{ij}^{q-p} \mathbf{p}_j + T_{ii}^{q-q} q_i + T_{ii}^{q-p} \mathbf{p}_i = -\chi_i$$

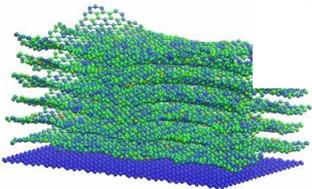
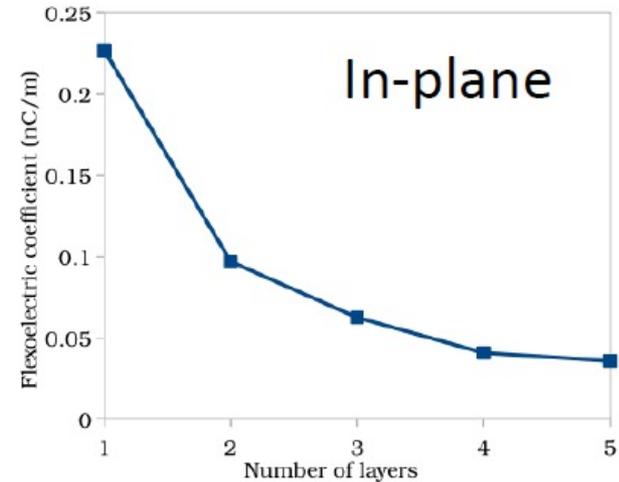
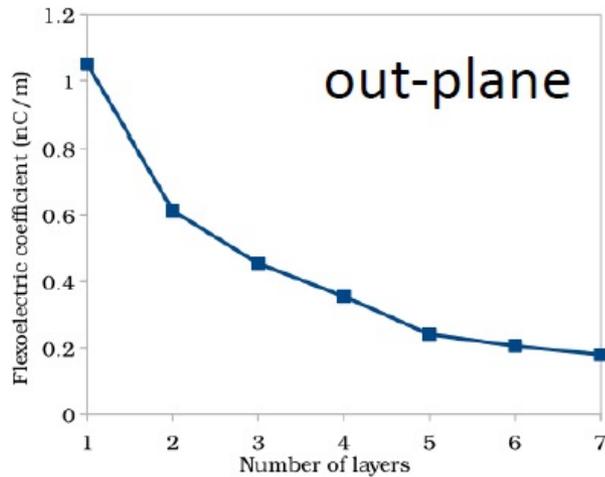
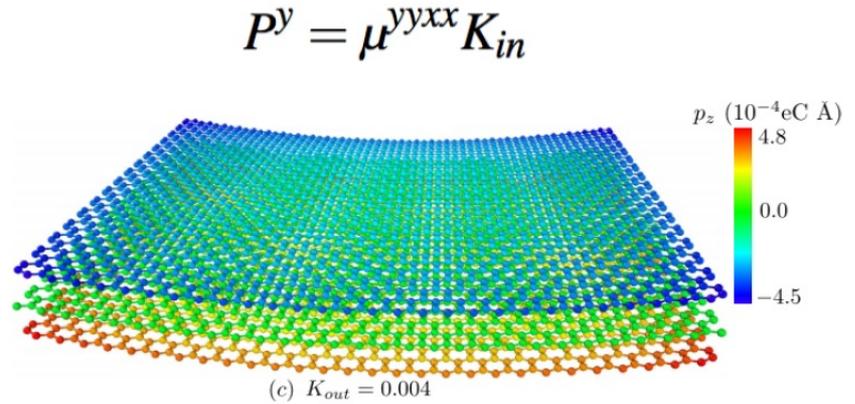
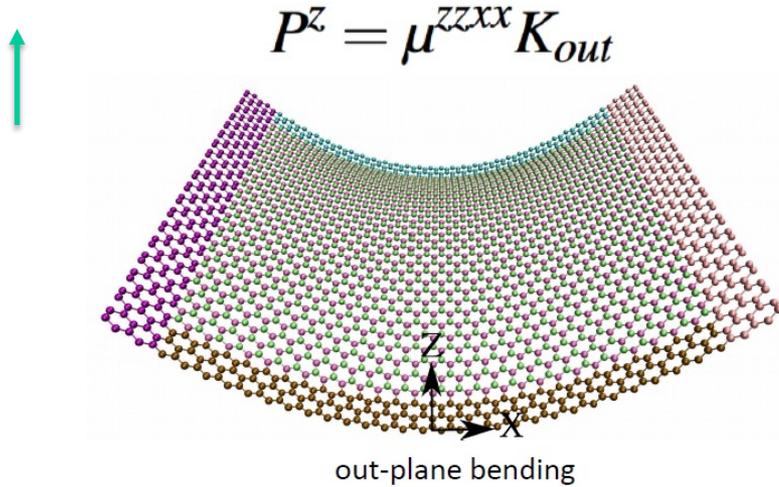
$$\sum_{j=1; i \neq j}^N T_{ij}^{q-p} q_j + \sum_{j=1; i \neq j}^N T_{ij}^{p-p} \mathbf{p}_j + T_{ii}^{q-p} q_i + T_{ii}^{p-p} \mathbf{p}_i = 0$$



Highly beneficial over DFT, wide scope for investigating large deformations

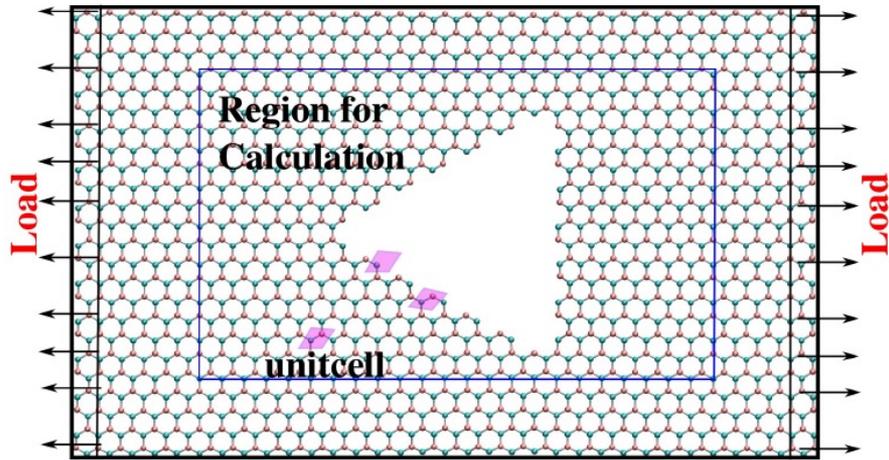
# Flexoelectric coefficient of graphene

## Charge dipole model

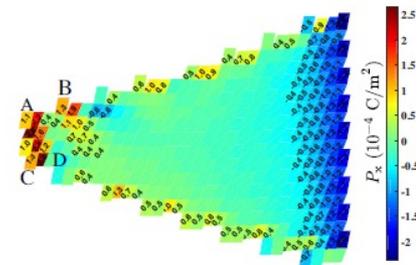
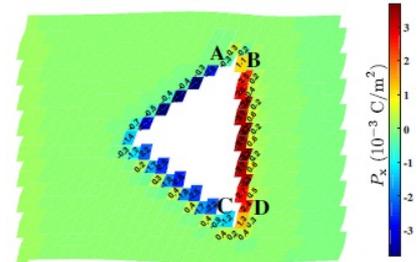
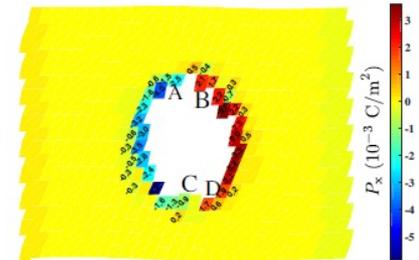
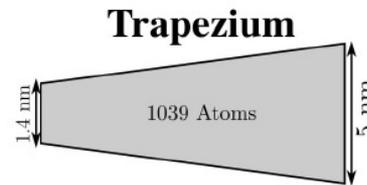
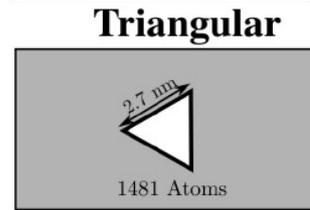
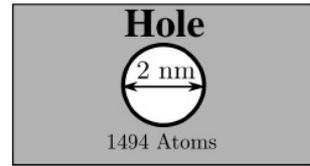
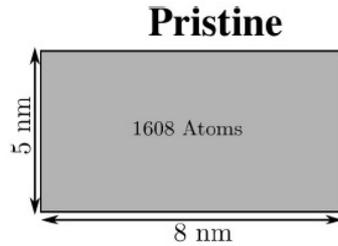
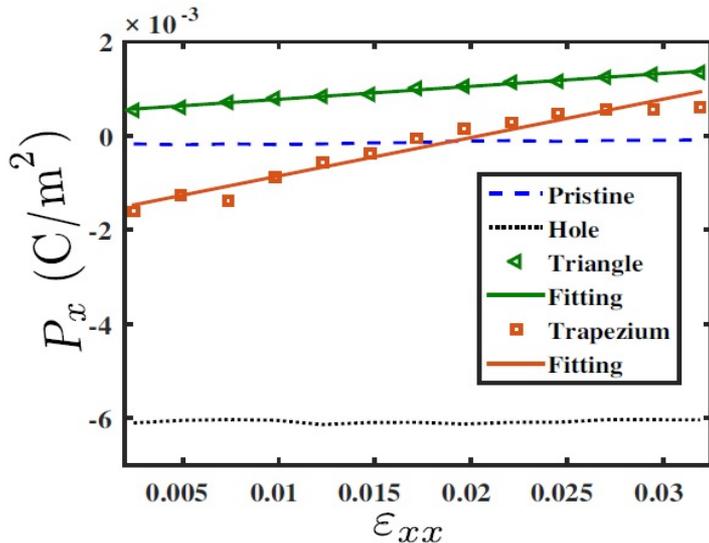


# Flexoelectric coefficient of graphene

## Charge dipole model



Schematic atomic configuration with loading conditions



Graphene with triangular defect

$$d_{xxx} = 0.02826 \text{ C/m}^2$$

$$\mathbf{P}_x^f = 5.01152 \times 10^{-4} \text{ C/m}^2$$

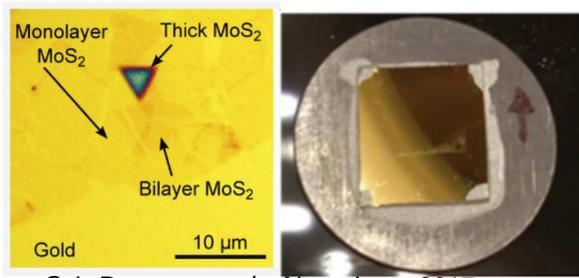
$$d_{xxx} = 0.08013 \text{ C/m}^2$$

$$\mathbf{P}_x^f = -16.67440 \times 10^{-4} \text{ C/m}^2$$

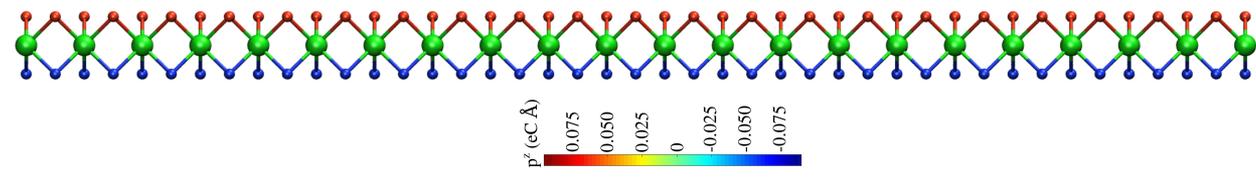
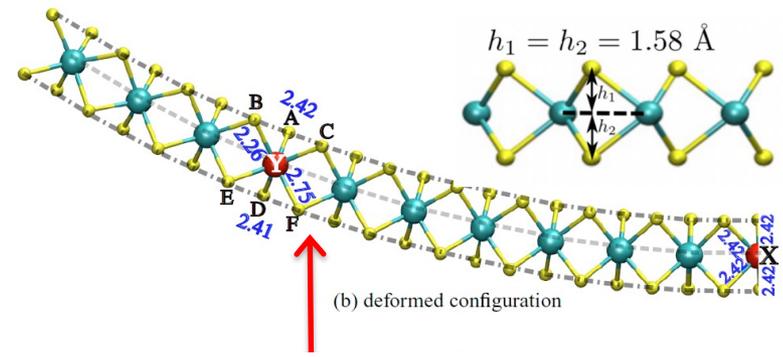
B. Javvaji, B. He and X. Zhuang. The generation of piezoelectricity and flexoelectricity in graphene by breaking the materials symmetries. Nanotechnology, 29: 225702, 2018.

# Flexoelectric coefficient of graphene

## Bending induced out of plane polarization

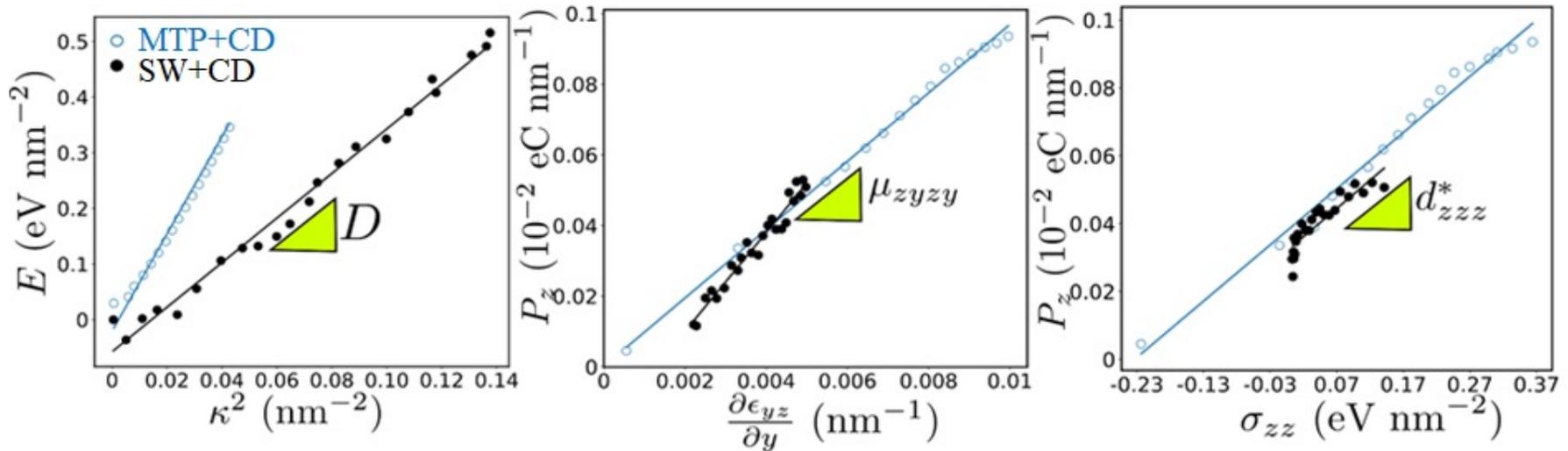


C.J. Brennan et al., Nano Lett. 2017



Response of MoS2 monolayer with SW potential and MTP potential

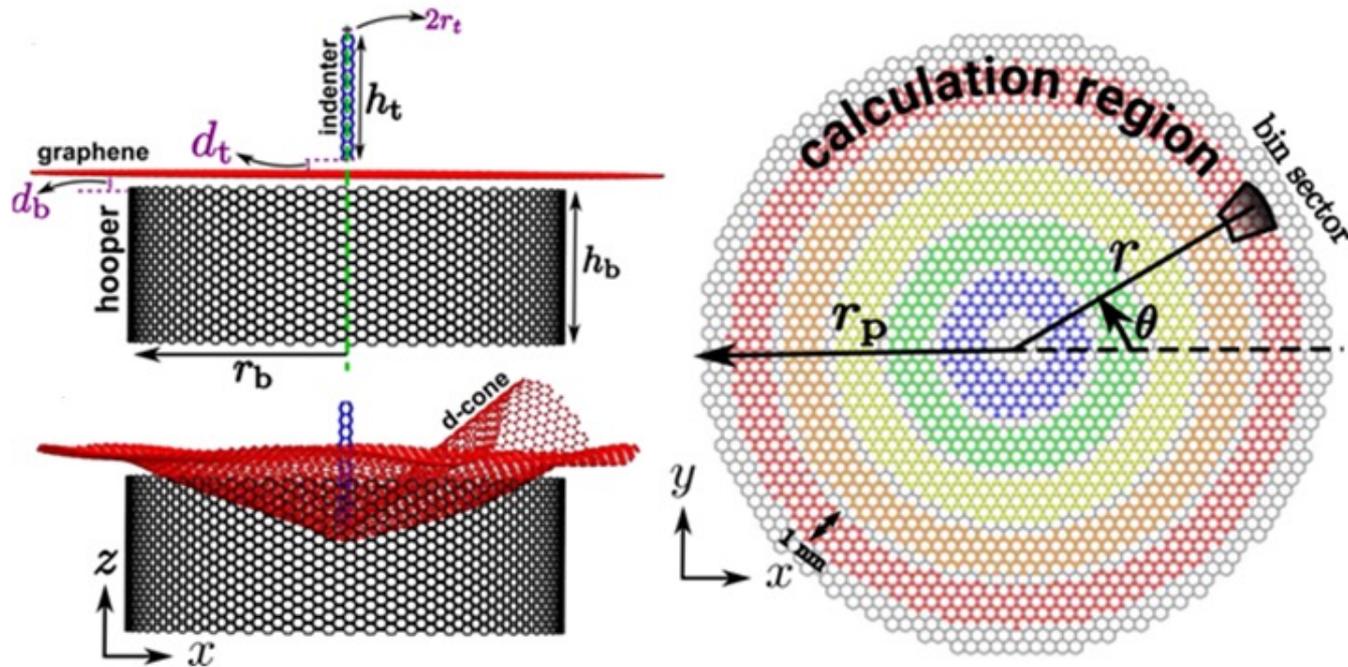
No change in CD parameters



The polarization response with strain gradient and with stress is highly linear

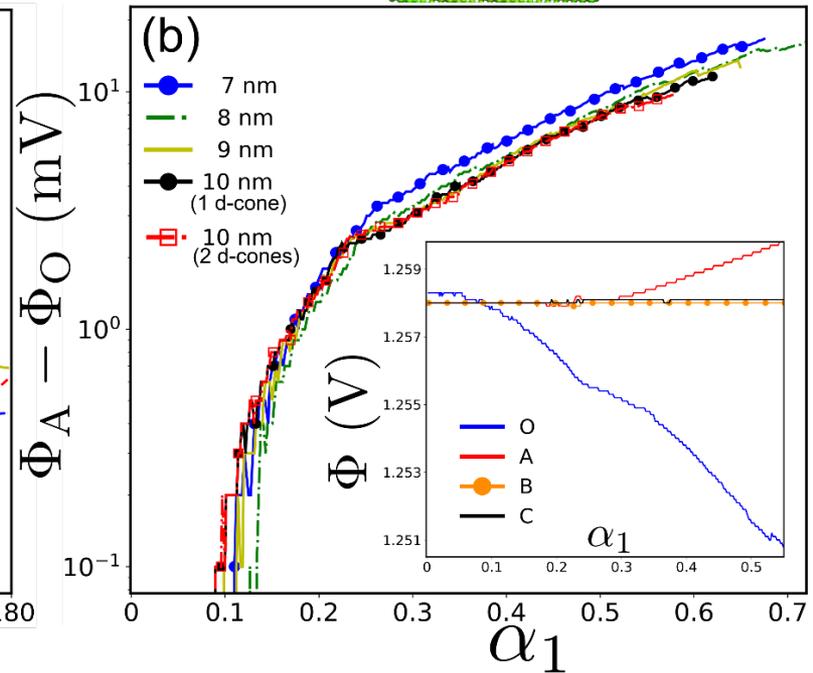
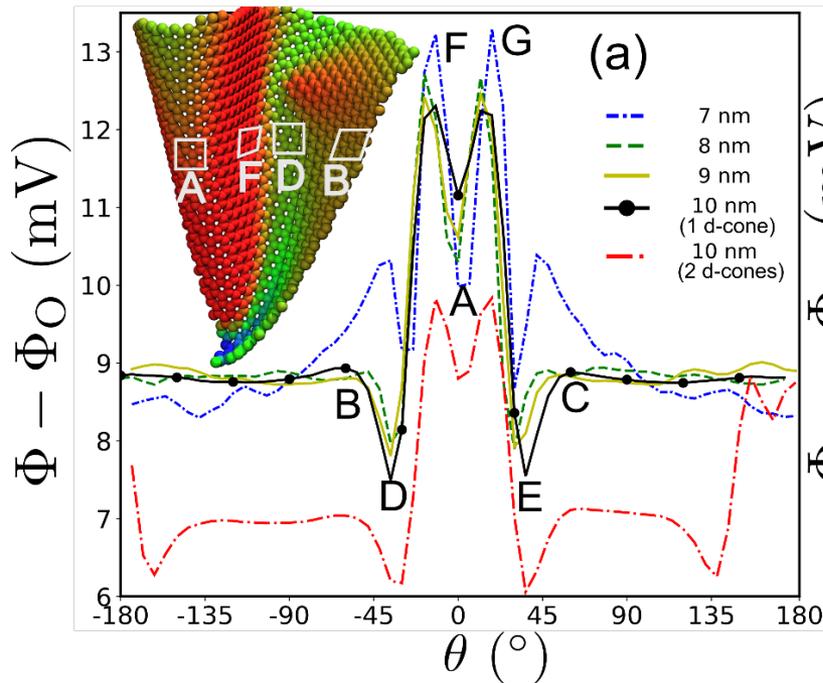
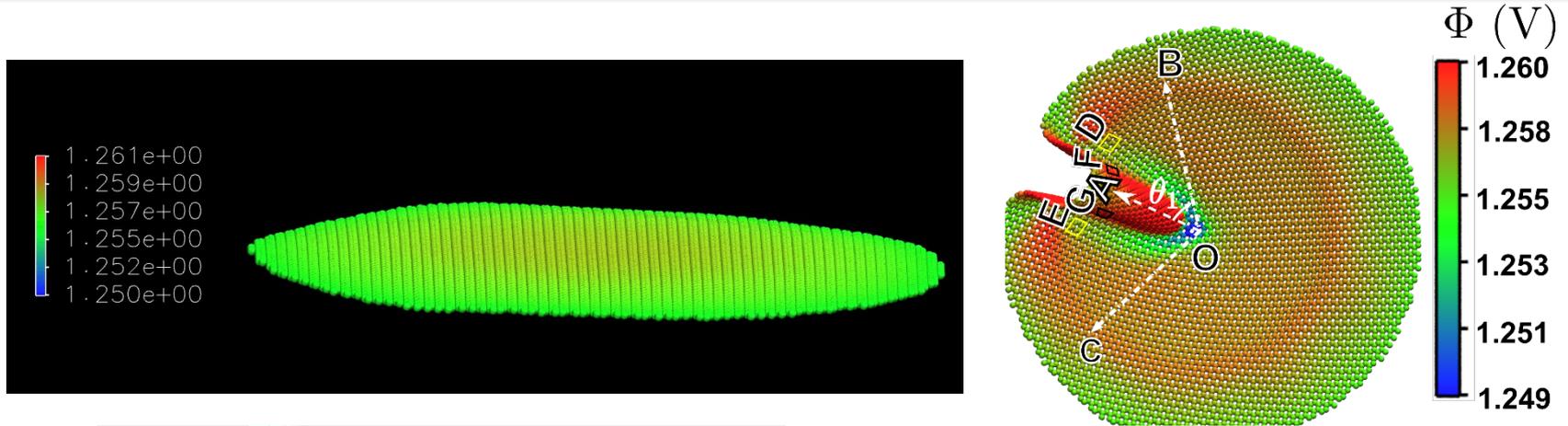
	<b>MTP+CD</b>	<b>SW+CD</b>	<b>Experimental results</b>
$\mu$ (nC/m)	<b>0.023</b>	0.025 (poor linear fitting issues)	0.091 (C.J. Brennan et al., Nano Lett. 2017)
$d_{33}^*$ (pm/V)	<b>1.64</b>	1.681 (poor linear fitting)	1-1.5 (C.J. Brennan et al., Nano Lett. 2017)
D (eV)	<b>16.51</b>	8.314	9 to 16 eV (several reports)
E (N/m)	<b>135</b>	100	130 to 180 (several reports)

**The results from MTP+CD model compare well with the experiments.**

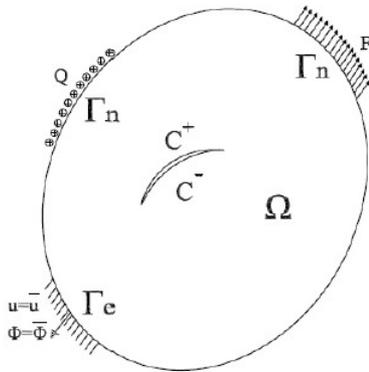


- Consider circular graphene nanoribbon as an example
- Hooper CNT held fixed and indenter moves with constant speed
- No other conditions are imposed
- Curvature variation confirms the d-cone structure due to crumpling

# Graphene crumpling response



- **Atomic-scale model of flexoelectric materials**
- **Nano-continuum scale model of flexoelectric structures**
- **Microscale model of flexoelectric composites**
- **Macroscale application with phonic topological insulator**



## Balance equations of electric and mechanical fields

$$\nabla \cdot \sigma + b = 0 \quad \text{in } \Omega$$

$$\nabla \cdot \mathbf{D} - q = 0 \quad \text{in } \Omega$$

$$\nabla_s \cdot \sigma_s = 0 \quad \text{on } \Gamma$$

$$\nabla_s \cdot D_s = 0 \quad \text{on } \Gamma$$

## Energy density function of flexoelectric materials

$$U = U_b + U_s$$

flexoelectric related terms

$$U_b = \frac{1}{2} \epsilon : \mathbf{C} : \epsilon - \mathbf{E} \cdot \mathbf{e} : \epsilon - \mathbf{E} \cdot \mathbf{h} : \dot{\eta} - \frac{1}{2} \mathbf{E} \cdot \boldsymbol{\kappa} \cdot \mathbf{E} + \frac{1}{2} \dot{\eta} : \mathbf{g} : \dot{\eta}$$

$$U_s = U_{s0} + \alpha_s : \epsilon_s + \omega_s \cdot \mathbf{E}_s + \frac{1}{2} \epsilon_s : \mathbf{C}_s : \epsilon_s - \mathbf{E}_s \cdot \mathbf{e}_s : \epsilon_s - \frac{1}{2} \mathbf{E}_s \cdot \boldsymbol{\kappa}_s \cdot \mathbf{E}_s$$

$g$ : the sixth order tensor of strain gradient elasticity

$h = d$ -f is the outcome of converse-flexoelectricity and flexoelectricity

$\eta$  is the strain gradient tensor

## Constitutive equations

$$\sigma^b = \sigma - \nabla \cdot \tau = \frac{\partial U_b}{\partial \epsilon} - \nabla \cdot \left( \frac{\partial U_b}{\partial \eta} \right) = C : \epsilon - E \cdot e + \nabla E : h$$

$$D^b = -D - \nabla \cdot Q = -\frac{\partial U_b}{\partial E} - \nabla \cdot \left( \frac{\partial U_b}{\partial \nabla E} \right) = e \cdot \epsilon + \kappa \cdot E + h : \dot{\eta}$$

$$\sigma_s = \tau_s + \mathbb{C}_s : \epsilon_s - e_s \cdot E_s$$

$$D_s = \omega_s + e_s^T : \epsilon_s + \kappa_s \cdot E_s$$

C and $\mathbb{C}_s$	fourth-order elastic bulk and surface stiffness tensors
e and $e_s$	bulk and surface piezoelectric third order tensors,
$\tau_s$ and $\omega_s$	residual surface stress and electric field.
$\epsilon$ and E	bulk strain tensor and bulk electric field vector
$\epsilon_s$ and $E_s$	corresponding surface counterparts.

Commercial FE software however provides only C0 continuity

$$U = U_b + U_s$$

$$U_b = \frac{1}{2} \boldsymbol{\epsilon} : \mathbf{C} : \boldsymbol{\epsilon} - \mathbf{E} \cdot \mathbf{e} : \boldsymbol{\epsilon} - \mathbf{E} \cdot \mathbf{h} : \boldsymbol{\eta} - \frac{1}{2} \mathbf{E} \cdot \boldsymbol{\kappa} \cdot \mathbf{E} + \frac{1}{2} \boldsymbol{\eta} : \mathbf{g} : \boldsymbol{\eta}$$

$$U_s = U_{s0} + \boldsymbol{\alpha}_s : \boldsymbol{\epsilon}_s + \boldsymbol{\omega}_s \cdot \mathbf{E}_s + \frac{1}{2} \boldsymbol{\epsilon}_s : \mathbf{C}_s : \boldsymbol{\epsilon}_s - \mathbf{E}_s \cdot \mathbf{e}_s : \boldsymbol{\epsilon}_s - \frac{1}{2} \mathbf{E}_s \cdot \boldsymbol{\kappa}_s \cdot \mathbf{E}_s$$

$C^1$  continuity

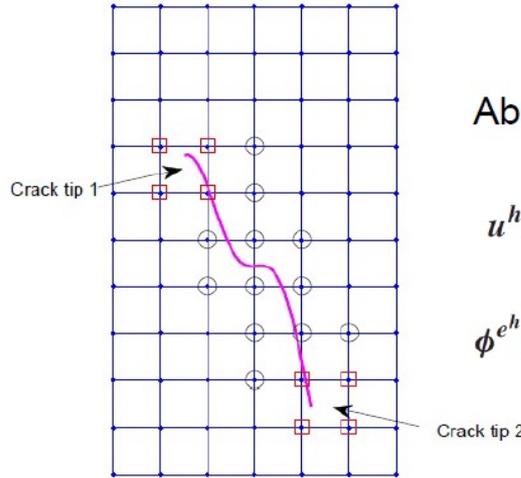
IGA (IsoGeometric Analysis)  
Based on non-uniform B-Splines

$$u_h(x, y) = \sum_{i=1}^{ncp} \sum_{j=1}^{mcp} N_{i,j}^{p,q}(\xi, \eta) u_{ij}^e = (\mathbf{N}_u)^T \mathbf{u}^e$$

$$\theta_h(x, y) = \sum_{i=1}^{ncp} \sum_{j=1}^{mcp} N_{i,j}^{p,q}(\xi, \eta) \theta_{ij}^e = (\mathbf{N}_\theta)^T \boldsymbol{\theta}^e$$

Alternatively, one can use meshless methods

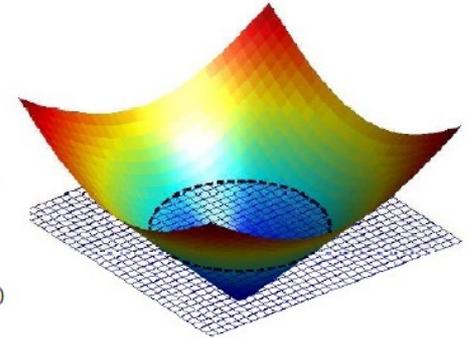
The displacement field,  $\mathbf{u}^h$  and electric potential field,  $\phi^h$  for a piezoelectric material in the XFEM formulation are expressed as:



Abs enrichment

$$\mathbf{u}^h(\mathbf{X}) = \sum_{i \in I} N_i(\mathbf{X}) \mathbf{u}_i + \sum_{N=1}^{n_c} \sum_{l \in L} N_l(\mathbf{X}) \mathbf{a}_l^{(N)} f_l^{(N)}$$

$$\phi^h(\mathbf{X}) = \sum_{i \in I} N_i(\mathbf{X}) \phi_i^e + \sum_{N=1}^{n_c} \sum_{l \in L} N_l(\mathbf{X}) \alpha_l^{(N)} f_l^{(N)}$$



$$\mathbf{u}^h(x) = \sum_{i \in I} N_i(\mathbf{X}) \mathbf{u}_i + \sum_{N=1}^{n_c} \sum_{j \in J} N_j(\mathbf{X}) \alpha_j^{(N)} \psi_I^{(N)} + \sum_{M=1}^{m_t} \sum_{k \in K} N_k(\mathbf{X}) \left( \sum_{i=1}^4 \Phi_i^{(M)}(r, \theta) b_k^i \right)$$

$$\phi^h(x) = \sum_{i \in I} N_i(\mathbf{X}) \phi_i + \sum_{N=1}^{n_c} \sum_{j \in J} N_j(\mathbf{X}) \alpha_j^{(N)} \psi_I^{(N)} + \sum_{M=1}^{m_t} \sum_{k \in K} N_k(\mathbf{X}) \left( \sum_{i=1}^4 \Phi_i^{(M)}(r, \theta) \beta_k^i \right)$$

$$\begin{bmatrix} \mathbf{K}^{UU} \\ \mathbf{K}^{U\Phi} \end{bmatrix} \begin{Bmatrix} u \\ a \end{Bmatrix} + \begin{bmatrix} \mathbf{K}^{U\Phi} \\ \mathbf{K}^{\Phi\Phi} \end{bmatrix} \begin{Bmatrix} \phi^e \\ \alpha \end{Bmatrix} = \begin{Bmatrix} f_u \\ f_u^a \end{Bmatrix}$$

$$\begin{bmatrix} \mathbf{K}^{\Phi U} \\ \mathbf{K}^{\Phi\Phi} \end{bmatrix} \begin{Bmatrix} u \\ a \end{Bmatrix} - \begin{bmatrix} \mathbf{K}^{U\Phi} \\ \mathbf{K}^{\Phi\Phi} \end{bmatrix} \begin{Bmatrix} \phi^e \\ \alpha \end{Bmatrix} = \begin{Bmatrix} f_\phi \\ f_\phi^\alpha \end{Bmatrix}$$

Discrete equations for coupling between stress and polarization

- Shape deriv. and level sets to find geometry with min. compliance
- Shape deriv. as normal velocity of free boundary
- Front propagation by solution of Hamilton-Jacobi equation for a level set function
- Shape is capture on a fixed Eulerian mesh.

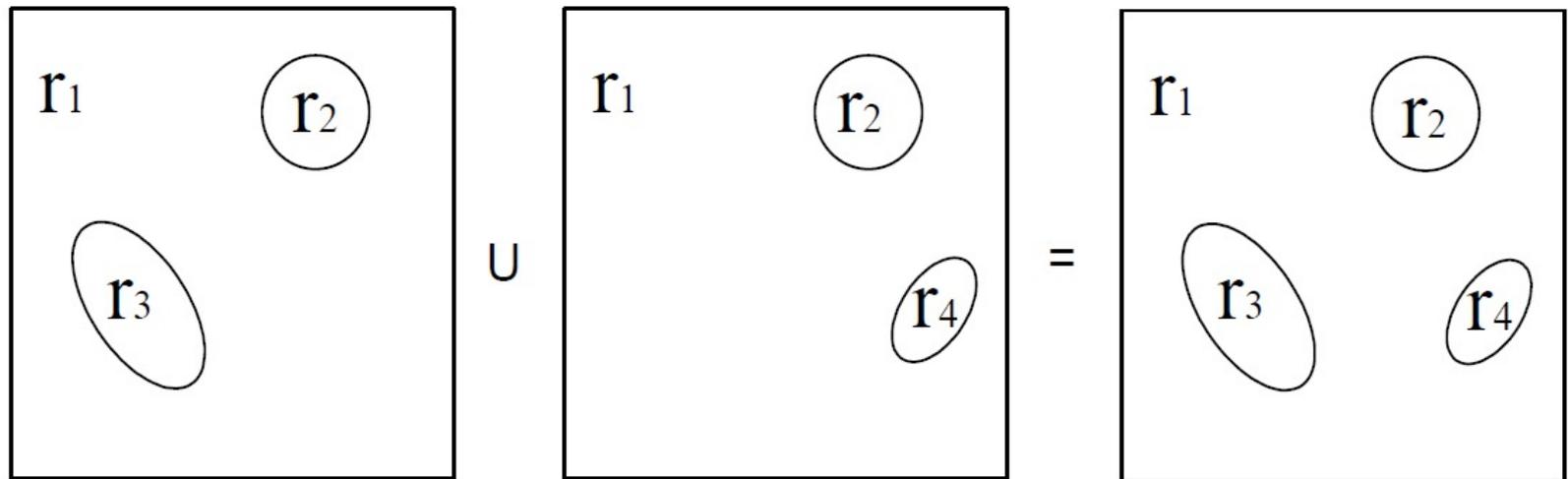


Figure: Multiple level sets representation : The union of two level set functions,  $\phi_1$  and  $\phi_2$  gives the actual domain with inclusions.

Single level set

$$r = \frac{1}{2}[r_1(1 + \text{sign}(\Phi)) + r_2(1 - \text{sign}(\Phi))].$$

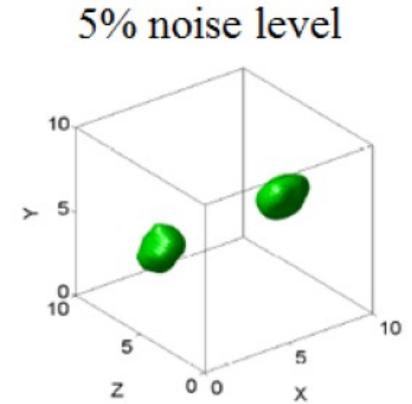
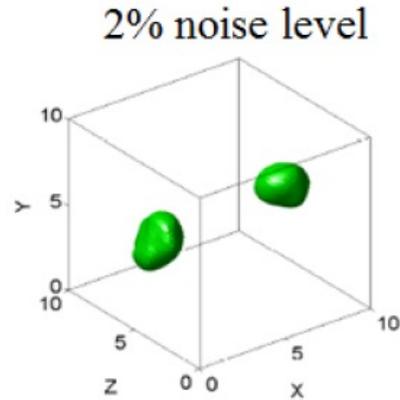
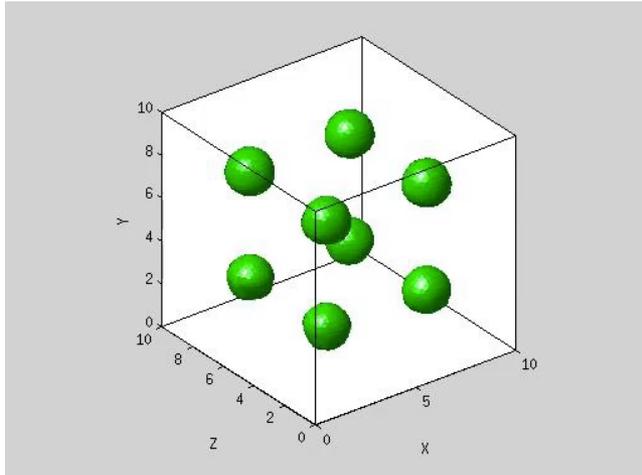
Multiple level sets

$$r = \frac{1}{4}[r_1(1 + S_1)(1 + S_2) + r_2(1 - S_1)(1 - S_2) + r_3(1 - S_1)(1 + S_2) + r_4(1 + S_1)(1 - S_2)]$$

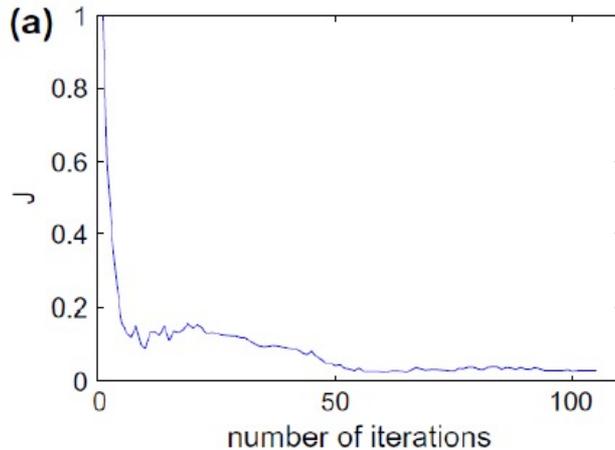
$S_1$  and  $S_2$  correspond to the sign of the level set functions  $\phi_1$  and  $\phi_2$  respectively.  $r_1$ ,  $r_2$ ,  $r_3$  and  $r_4$  are material ratios in the four regions.

# Robustness of level sets in modelling

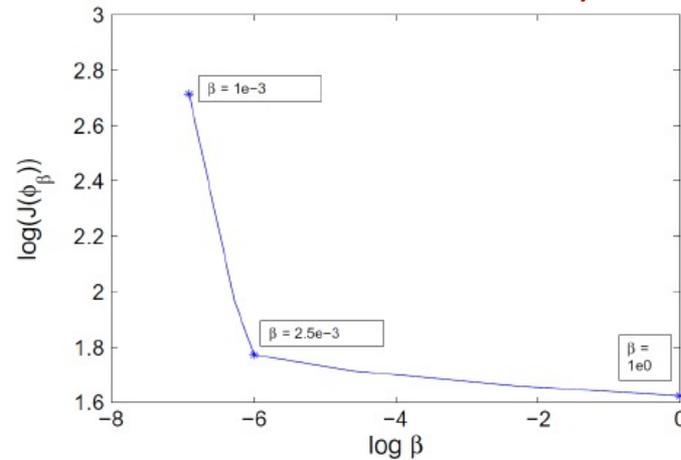
The level set method is suitable for **highly evolving geometry**



Convergence to objective func.



L- curve for stability



## Electromechanical coupling coefficient

$$k^2 = \frac{\Pi_e}{\Pi_m}$$

$$\Pi_e = \frac{1}{2} \int_{\Omega} \mathbf{E}(\phi)^T \boldsymbol{\kappa} \mathbf{E}(\phi) d\Omega + \frac{1}{2} \int_{\Gamma} \mathbf{E}^s(\phi)^T \boldsymbol{\kappa}^s \mathbf{E}^s(\phi) d\Gamma = \frac{1}{2} \phi^T (\mathbf{K}_{\phi\phi} + \mathbf{K}_{\phi\phi}^s) \phi$$

$$\Pi_m = \frac{1}{2} \int_{\Omega} \boldsymbol{\epsilon}(\mathbf{u})^T \mathbf{C} \boldsymbol{\epsilon}(\mathbf{u}) d\Omega + \frac{1}{2} \int_{\Gamma} \boldsymbol{\epsilon}^s(\mathbf{u})^T \mathbf{C}^s \boldsymbol{\epsilon}^s(\mathbf{u}) d\Gamma = \frac{1}{2} \mathbf{u}^T (\mathbf{K}_{uu} + \mathbf{K}_{uu}^s) \mathbf{u}$$

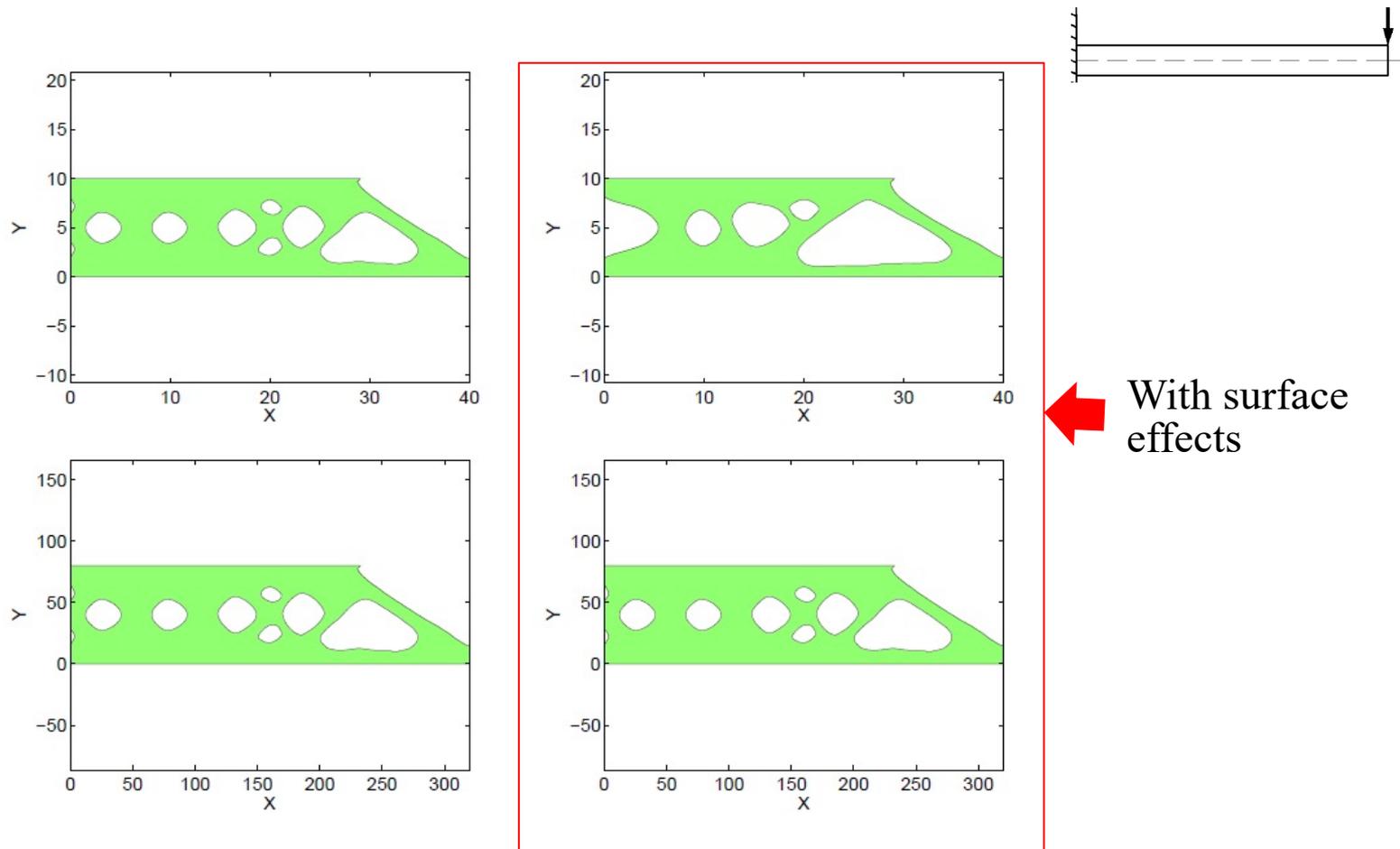
## Objective function and constraints

$$\text{Minimize } J(\Psi) = \frac{1}{k^2} = \frac{\Pi_m}{\Pi_e}$$

$$\text{Subject to } \int_{\Omega} d\Omega - \bar{V} = 0$$

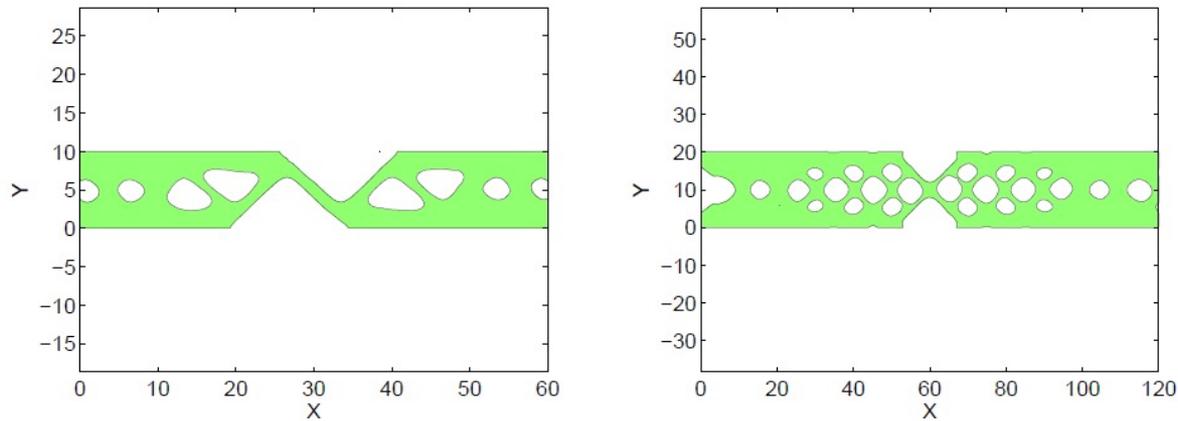
$$\text{and } \delta\Pi = 0$$

# Surface effects plays the role over sizes

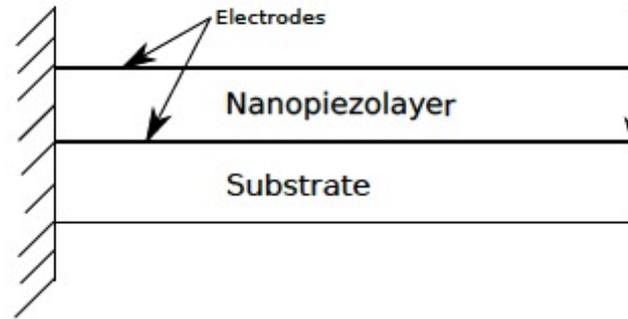


**Figure:** The optimal topology obtained for  $J$  objective function for 40x10 nm and 320x80 nm cantilever beams without surface effects left and with surface effects right.

# Surface effects plays the role over sizes



**Figure:** Optimal topology for objective function  $J$  for (a) 60x10 nm and (b) 120x20 nm fixed nanobeam.



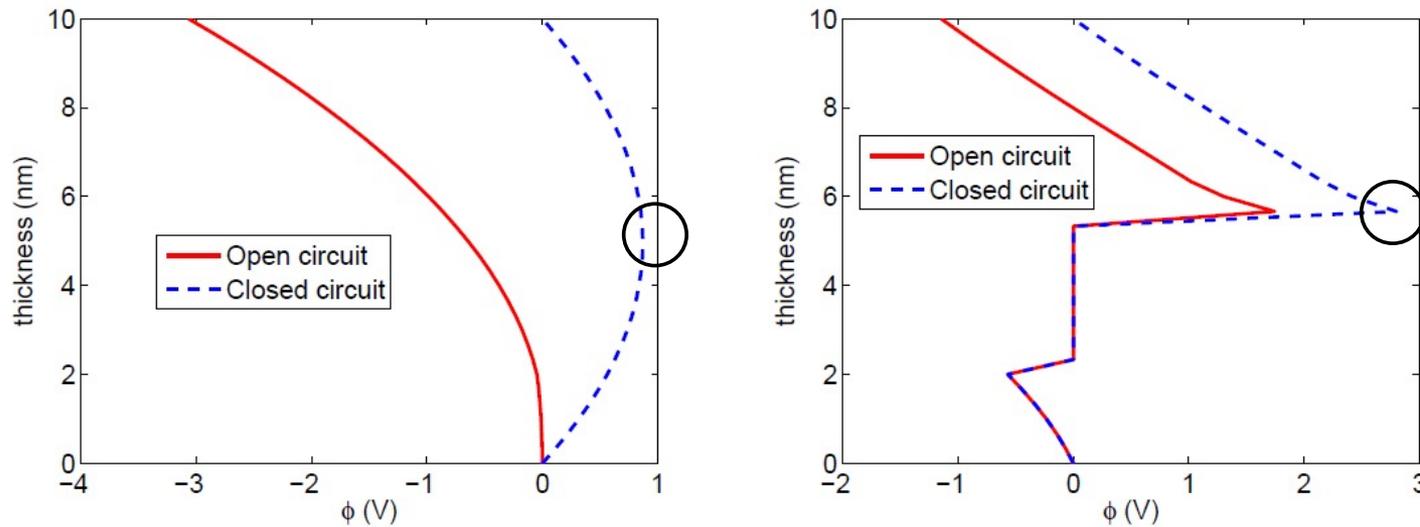
boundary conditions and sizes effects are most dominant factors

**Open circuit**

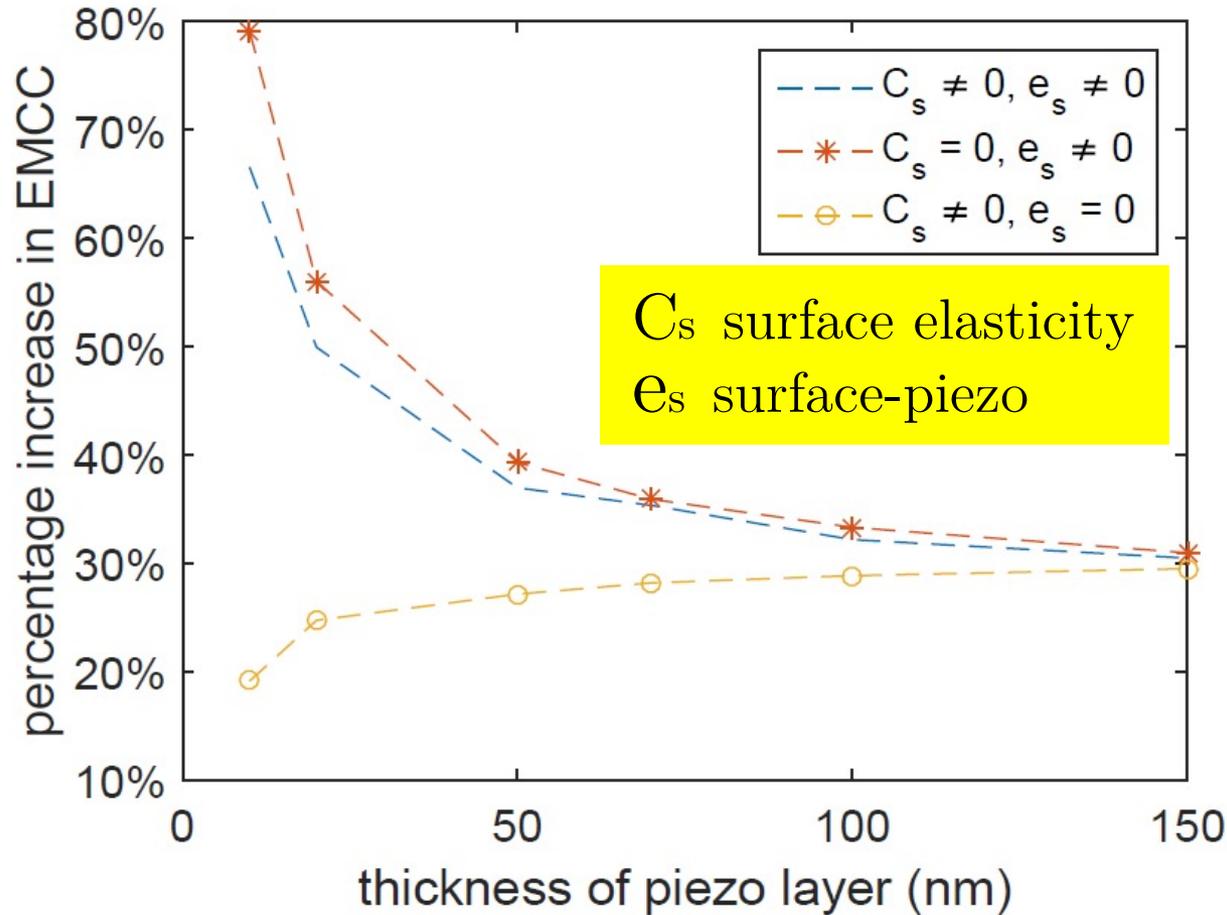
size	nominal EMCC ( $C^s \neq 0, e^s \neq 0$ )
<b>Aspect ratio = 4</b>	
40 × 10	1.19
80 × 20	1.13
160 × 40	1.1
<b>Aspect ratio = 8</b>	
80 × 10	1.15
160 × 20	1.095
240 × 30	1.06

**Closed circuit**

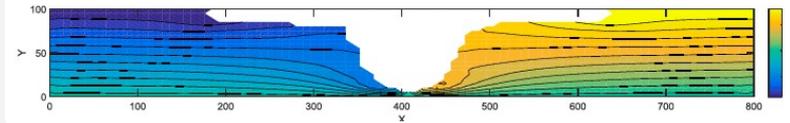
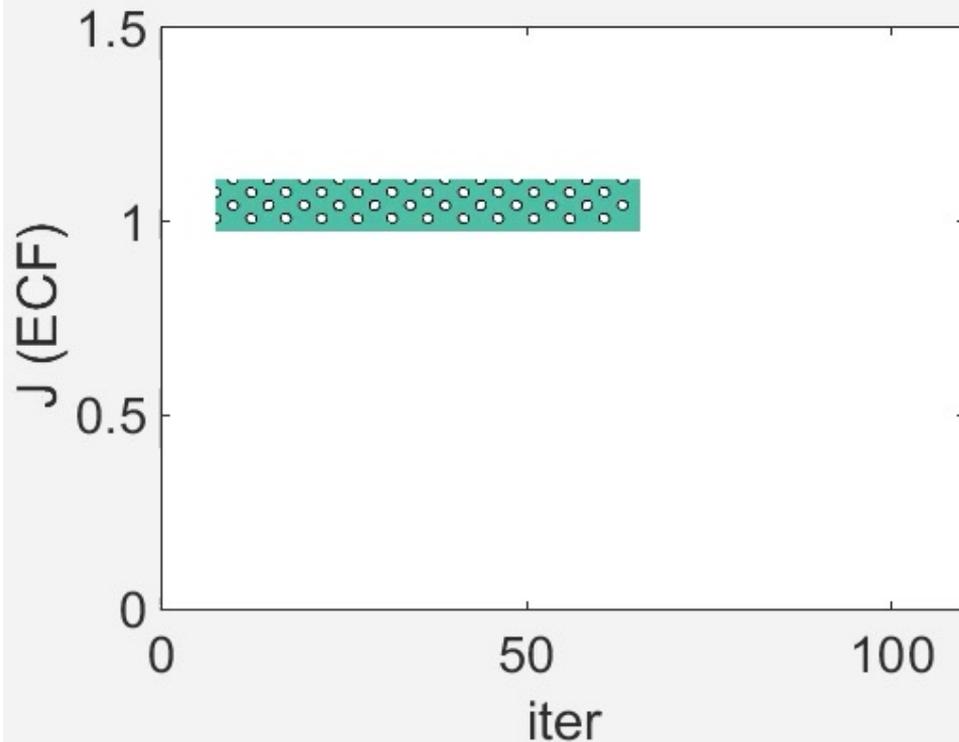
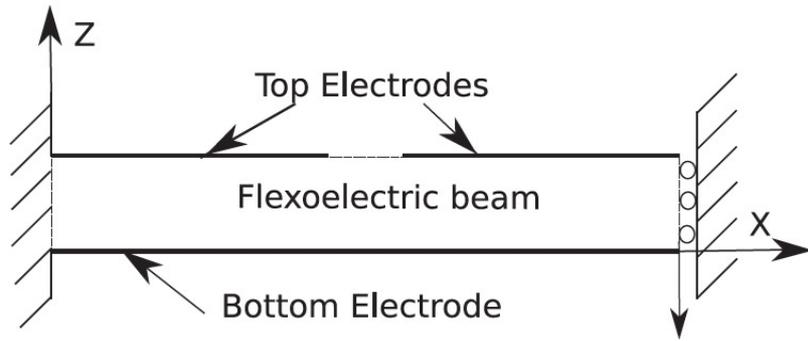
size	nominal EMCC ( $C^s \neq 0, e^s \neq 0$ )
<b>Aspect ratio = 4</b>	
40 × 10	2.5
80 × 20	2.2
160 × 40	2.1
<b>Aspect ratio = 8</b>	
80 × 10	2.6
160 × 20	2.3
240 × 30	2.2

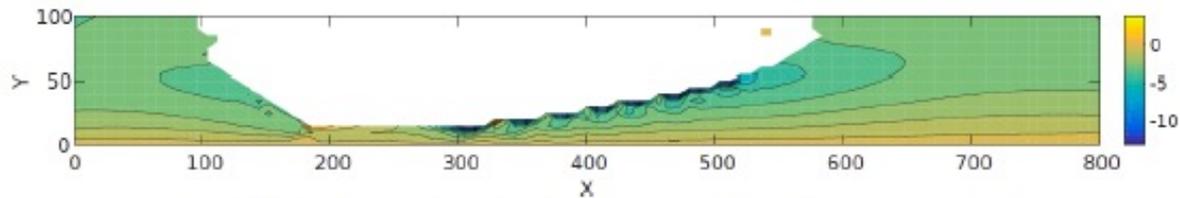
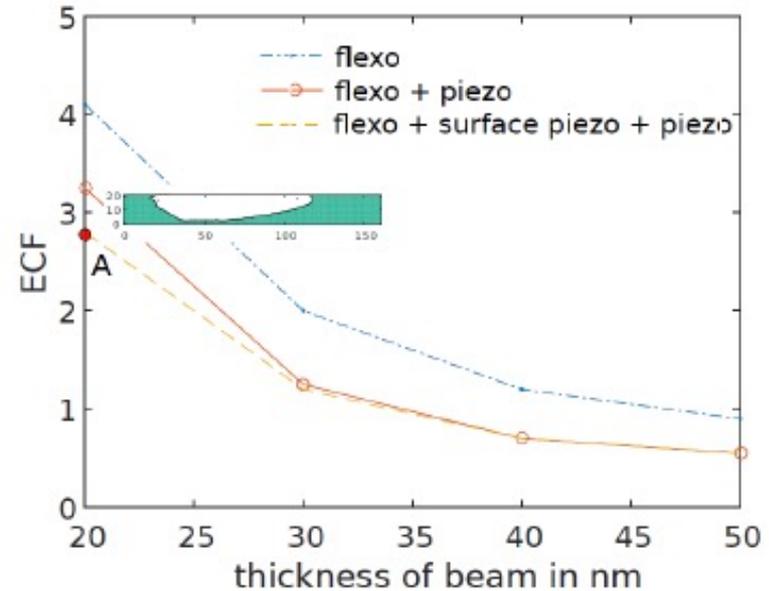
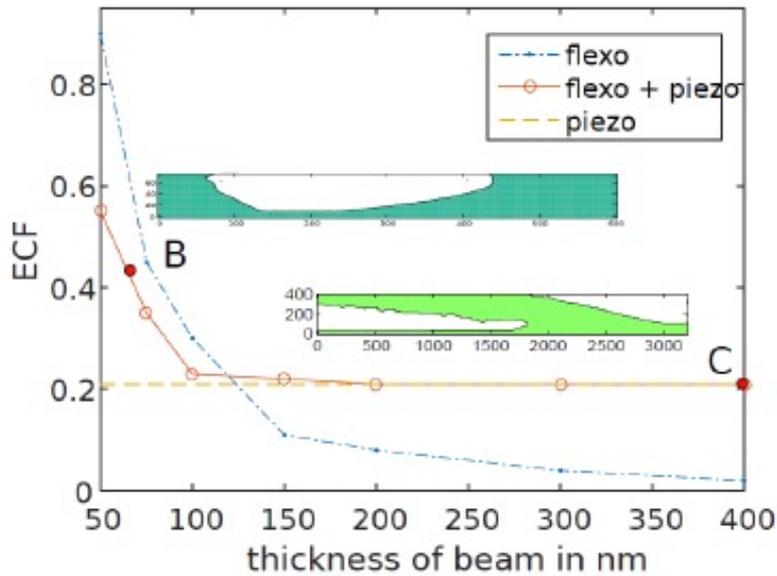


**Figure:** Electric potential distribution across the thickness of the  $40 \times 10$  nm, (a) Solid beam (b) Optimal beam, at  $x = 10$  nm.



# BTO plate topology optimization wrt ECC

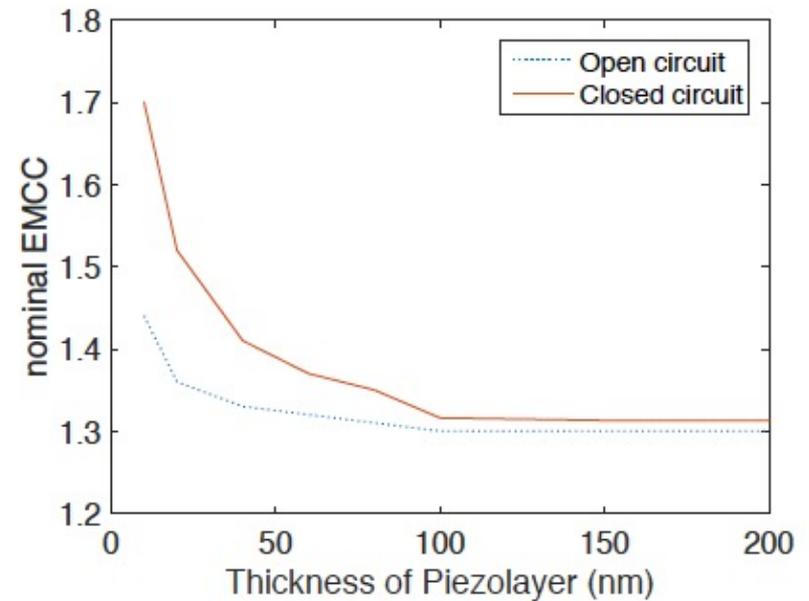
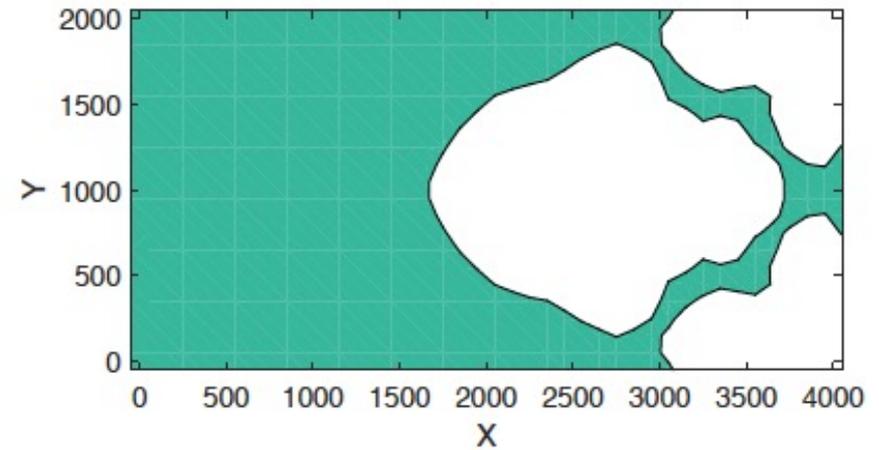
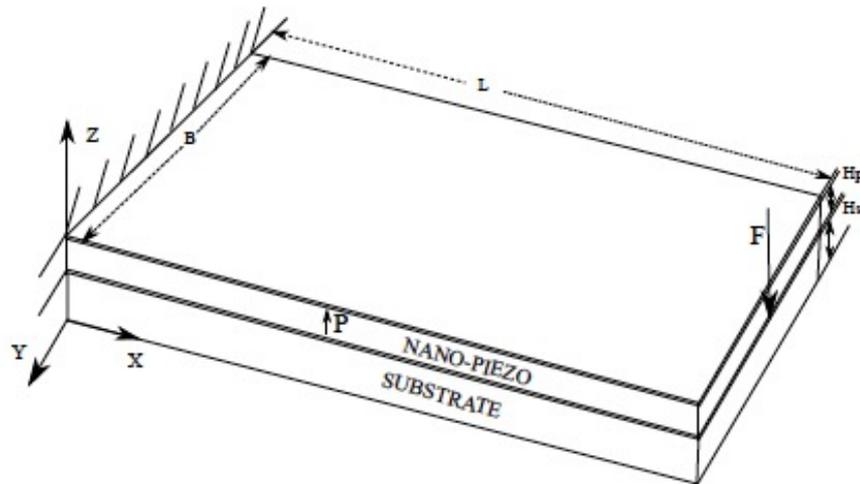




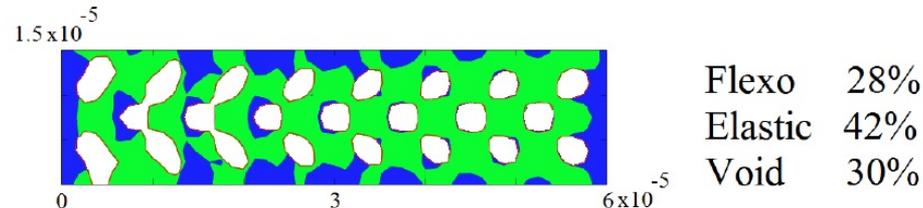
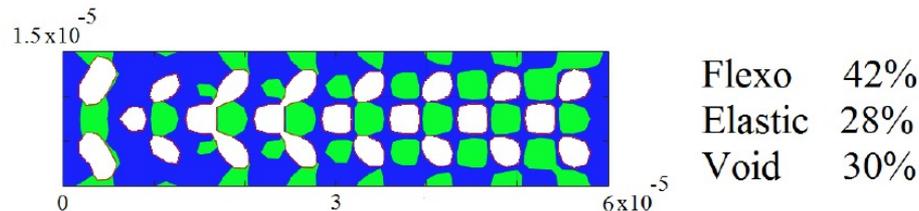
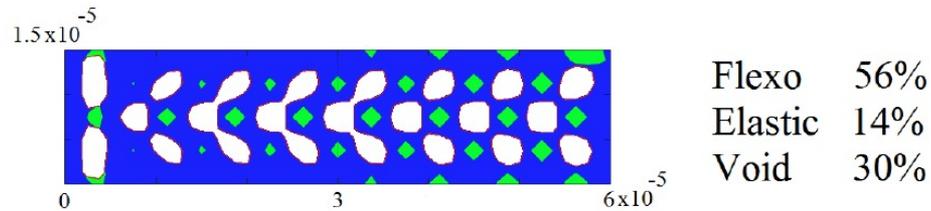
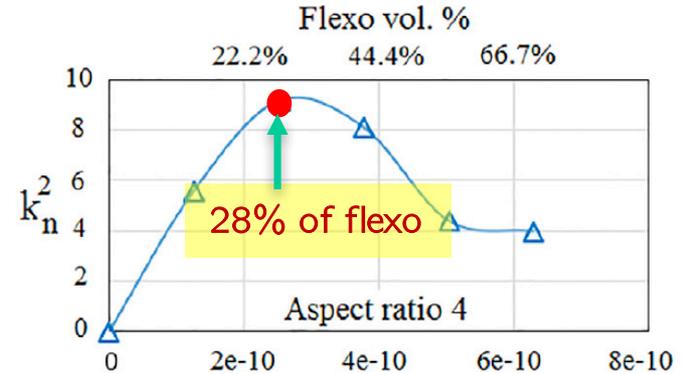
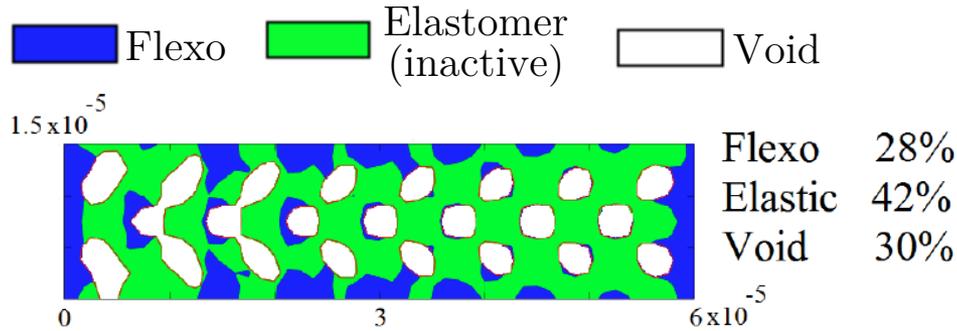
Distribution of electric potential

# Plate energy harvester

$$\begin{aligned} \nabla \cdot \boldsymbol{\sigma} + \boldsymbol{b} &= 0 && \text{in } \Omega \\ \nabla \cdot \boldsymbol{D} - q &= 0 && \text{in } \Omega \\ \nabla_s \cdot \boldsymbol{\sigma}_s &= 0 && \text{on } \Gamma \\ \nabla_s \cdot \boldsymbol{D}_s &= 0 && \text{on } \Gamma \end{aligned}$$



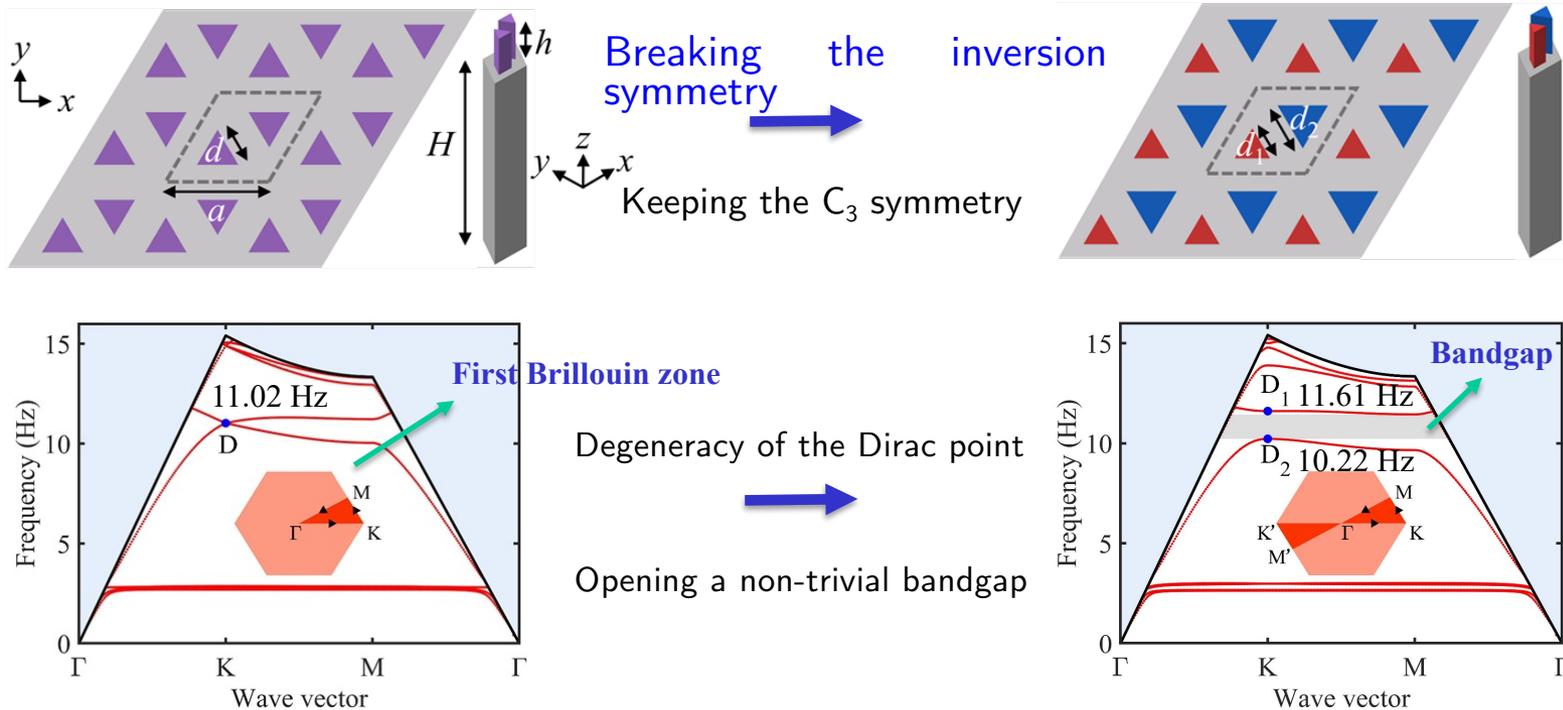
# Design of flexoelectric energy harvester



IGA (IsoGeometric Analysis)  
Based on non-uniform B-Splines

- Atomic-scale model of flexoelectric materials
- Nano-continuum scale model of flexoelectric structures
- Microscale model of flexoelectric composites
- **Macroscale application with phonic topological insulator**

- For low-frequency surface wave manipulation, we design a honeycomb lattice of pillars on the surface of elastic medium.
- Induced non-trivial bandgap can **provide robust surface wave attenuation**.

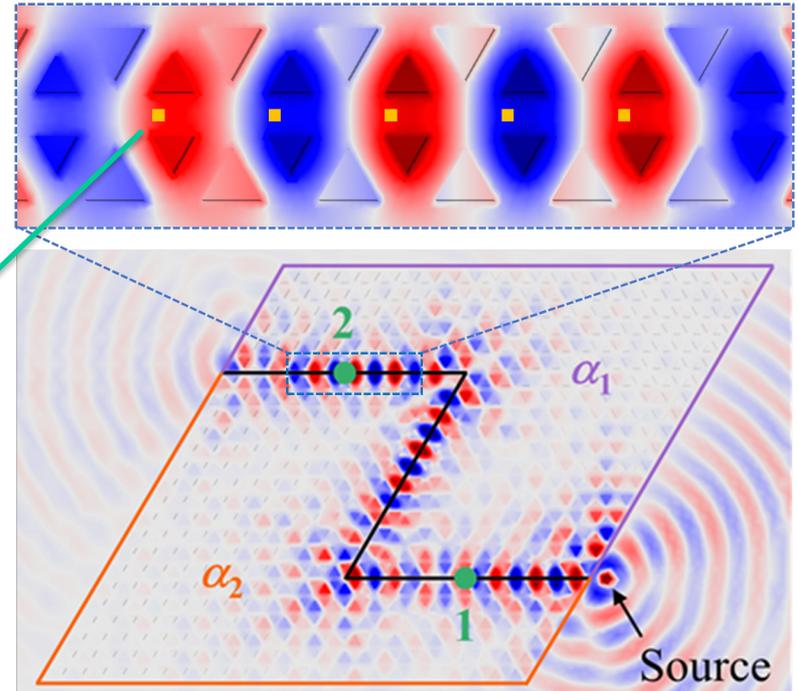
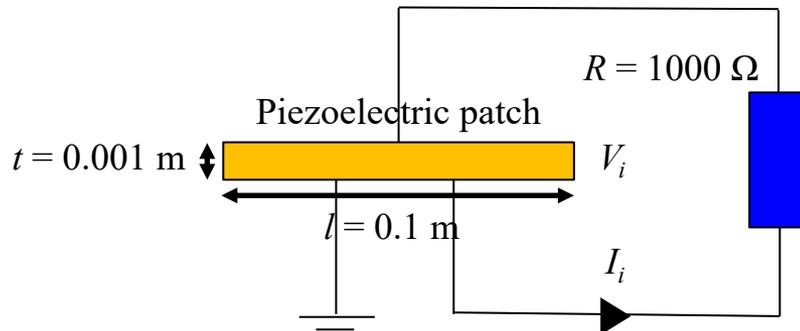


$a$ (m)	$d$ (m)	$d_1$ (m)	$d_2$ (m)	$h$ (m)	$H$ (m)
2.0	0.8	0.7	0.8	2.0	30.0

- A point source out-of-plane vibration is excited at the entrance of the zig-zag interface for **transmission** calculation.
- With the electro-mechanical coupling effect, the vibrating energy can be transformed to **electric power** by the square PZT patches attached to the top surface of soil.
- A simple circuit powered by each PZT patch with a resistance  $R$  is devised, whose average output power  $P_i$  is calculated by

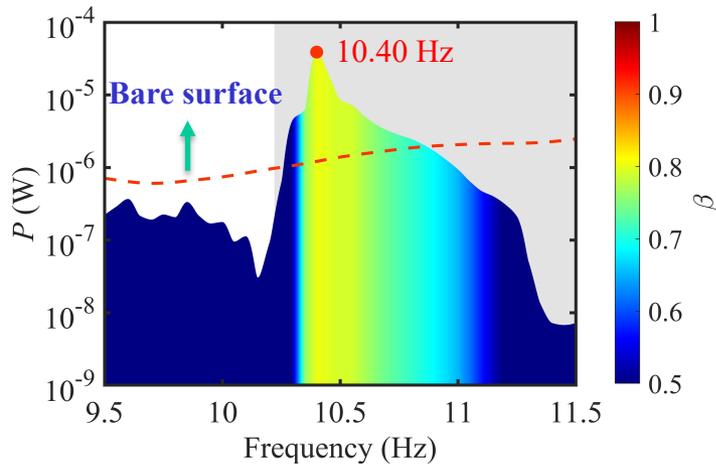
$$P_i = \frac{V_i}{\sqrt{2}} \frac{I_i}{\sqrt{2}} = \frac{R I_i^2}{2}$$

$$\text{The total power } P = \sum_{i=1}^5 P_i$$

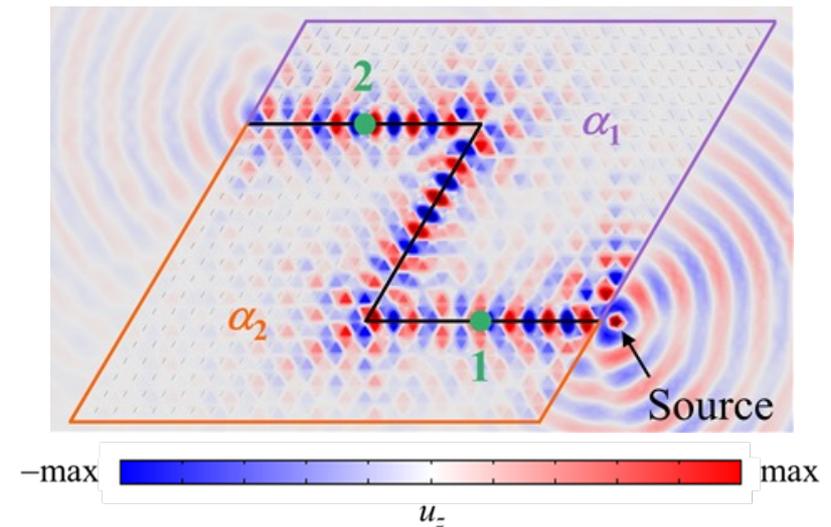


- The topological edge state within the frequency range (10.33, 10.97) Hz.
- At 10.40 Hz, the S-S interface supports high transmission and backscattering immunity of the topological edge state.
- It is more than **one order of magnitude higher than that of a bare surface**, showing a big advantage of the **energy harvesting** by topological edge state.

Piezoelectric energy harvesting for the edge states



Out-of-plane displacement fields at 10.40 Hz



## Review

Yabin Jin\*, Liangshu He, Zihui Wen, Bohayra Mortazavi, Hongwei Guo, Daniel Torrent, Bahram Djafari-Rouhani, Timon Rabczuk, Xiaoying Zhuang\* and Yan Li\*

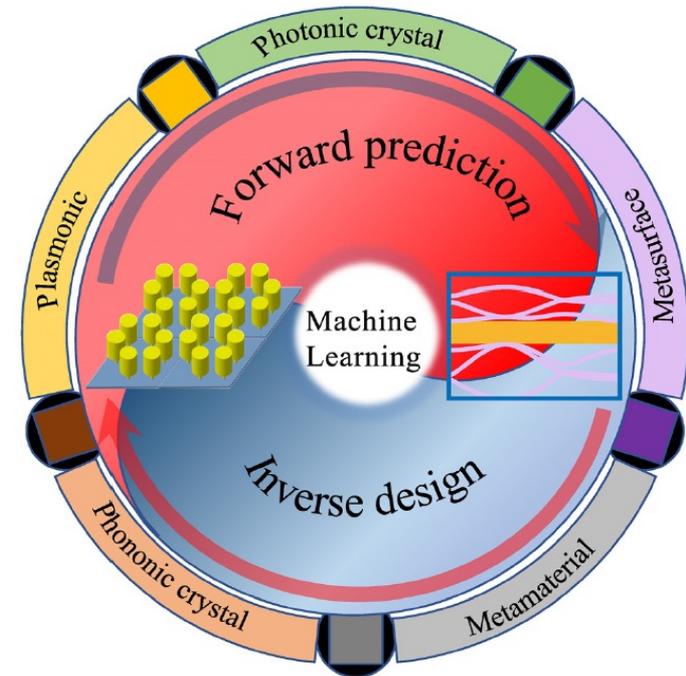
## Intelligent on-demand design of phononic metamaterials

<https://doi.org/10.1515/nanoph-2021-0639>  
Received October 28, 2021; accepted December 14, 2021;  
published online January 4, 2022

**Abstract:** With the growing interest in the field of artificial materials, more advanced and sophisticated functionalities are required from phononic crystals and acoustic metamaterials. This implies a high computational effort and cost, and still the efficiency of the designs may be not sufficient. With the help of third-wave artificial intelligence technologies, the design schemes of these materials are undergoing a new revolution. As an important branch of artificial intelligence, machine learning paves the way to new technological innovations by stimulating the exploration of structural design. Machine learning provides a powerful means of achieving an efficient and accurate design process by exploring nonlinear physical patterns in

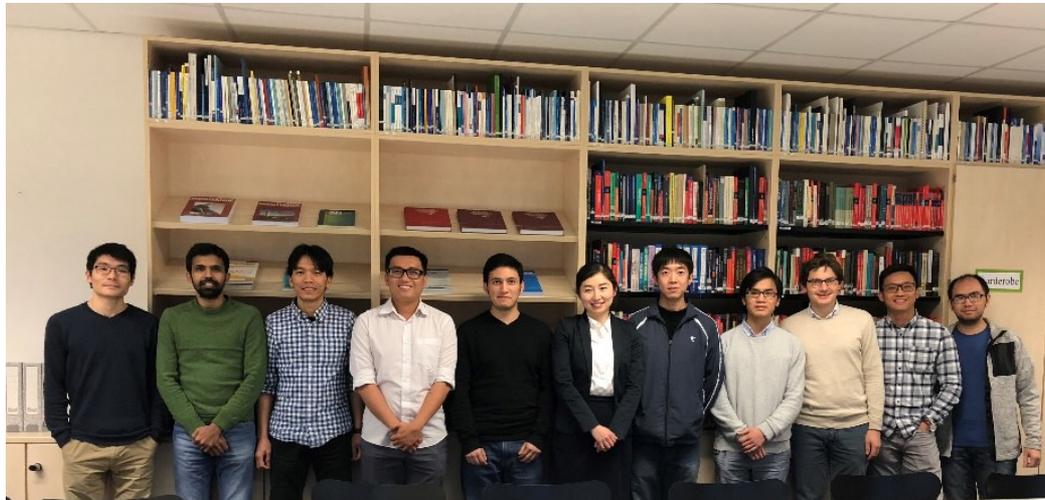
high-dimensional space, based on data sets of candidate structures. Many advanced machine learning algorithms, such as deep neural networks, unsupervised manifold clustering, reinforcement learning and so forth, have been widely and deeply investigated for structural design. In this review, we summarize the recent works on the combination of phononic metamaterials and machine learning. We provide an overview of machine learning on structural design. Then discuss machine learning driven on-demand design of phononic metamaterials for acoustic and elastic waves functions, topological phases and atomic-scale phonon properties. Finally, we summarize the current state of the art and provide a prospective of the future development directions.

**Keywords:** 2D materials; hierarchical structure; inverse design; machine learning; metamaterials; phononic crystals.



# Thank you your attention

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